LSF010x 1/2/8 Channel Auto-Bidirectional Multi-Voltage Level Translator for Open-Drain and Push-Pull Applications

1 Features

- Provides bidirectional voltage translation with no direction pin
- Supports up to 100-MHz up translation and greater than 100-MHz down translation at ≤ 30 pF cap load and up To 40-MHz up/down translation at 50 pF cap load
- Allows bidirectional voltage-level translation between
  - 0.95 V ↔ 1.8/2.5/3.3/5 V
  - 1.2 V ↔ 1.8/2.5/3.3/5 V
  - 1.8 V ↔ 2.5/3.3/5 V
  - 2.5 V ↔ 3.3/5 V
  - 3.3 V ↔ 5 V
- Low standby current
- 5-V tolerance I/O port to support TTL
- Low R_{ON} provides less signal distortion
- High-impedance I/O pins for EN = Low
- Flow-through pinout for easy PCB trace routing
- Latch-up performance >100 mA per JESD 17
- –40°C to 125°C operating temperature range

2 Applications

- GPIO, MDIO, PMBus, SMBus, SDIO, UART, I²C, and other interfaces in telecom infrastructure
- Enterprise systems
- Communications equipment
- Personal electronics
- Industrial applications

3 Description

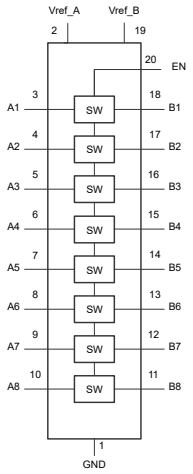
The LSF family of devices supports bidirectional voltage translation without the need for DIR pin which minimizes system effort (for PMBus, I²C, SMBus, and so forth). The LSF family of devices supports up to 100-MHz up translation and greater than 100-MHz down translation at ≤ 30 pF cap load and up to 40-MHz up/down translation at 50 pF cap load which allows the LSF family to support more consumer or telecom interfaces (MDIO or SDIO).

LSF family supports 5-V tolerance on I/O port which makes it compatible with TTL levels in industrial and telecom applications. The LSF family is able to set up different voltage translation levels on each channel which makes it very flexible.

Package Information

PART NUMBER	PACKAGE(1)	BODY SIZE (NOM)
LSF0101	SON (DRY, 6)	1.45 mm × 1.00 mm
	X2SON (DTQ, 6)	1.00 mm x 0.80 mm
LSF0102	X2SON (DQE, 8)	1.40 mm × 1.00 mm
	DSBGA (YZT, 8)	1.90 mm × 1.00 mm
	SM8 (DCT, 8)	2.80 mm × 2.95 mm
	VSSOP (DCU, 8)	2.30 mm × 2.00 mm
	SOT-23 (DDF, 8)	1.60 mm x 2.90 mm
LSF0108	VQFN (RKS, 20)	4.50 mm × 2.50 mm
	TSSOP (PW, 20)	4.40 mm × 6.50 mm
	VSSOP (DGS, 20)	3.00 mm x 5.10 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.



Functional Block Diagram

Table of Contents

4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision K (May 2021) to Revision L (November 2022)	Page
• Updated the *Applications* section	1
• Updated the *Description* section	1
• Updated the *Pin Configuration and Functions* section	4
• Added DDF and DGS packages.	4
• Updated the *Thermal Information* tables	8
• Updated *Electrical Characteristics* table	9
• Updated the *Functional Block Diagram* section	13
• Updated the *Auto Bidirectional Voltage Translation* section	13
• Updated the *Output Enable* section	14
• Updated the *Device Functional Modes* section	14
• Added the *Up and Down Translation* section	15
• Updated the *Application Information* section	16
• Updated the *Enable, Disable, and Reference Voltage Guidelines* section	17
• Added the *Bias Circuitry* section	17
• Added the *Single Supply Translation* section	20

Changes from Revision J (April 2020) to Revision K (May 2021)	Page
• Updated the numbering format for tables, figures, and cross-references throughout the document	1
• Updated the *Bidirectional Translation* section to include inclusive terminology	18

Changes from Revision I (June 2019) to Revision J (April 2020) **Page**

- Added section *Voltage Translation for Vref_B < Vref_A + 0.8 V* 22

Changes from Revision H (June 2019) to Revision I (July 2019) **Page**

- Changed product status from Advance Information mix to Production Data 1
- Deleted Advance Information note from the DTQ package in the Device Information table. 1
- Deleted Advance Information note from DTQ Package, in the Pin Configuration and Functions section. 4
- Deleted Advance Information note for the DTQ package in the Thermal Information table. 8

Changes from Revision G (February 2016) to Revision H (June 2019) **Page**

- Added Advance Information note to Device Information table for DTQ package 1
- Added DTQ6 pinout drawing to *Pin Configurations and Functions* section (Advance Information)..... 4
- Added Advance Information note to LSF0101 Thermal Information table. 8
- General improvements to Application and Implementation section for clarity. 16

Changes from Revision F (October 2015) to Revision G (October 2015) **Page**

- Added all available package dimensions in Device Information and changed the pin diagram description..... 1

Changes from Revision E (July 2015) to Revision F (October 2015) **Page**

- Changed Features from "Supports High Speed Translation, Greater Than 100 MHz" to "Supports Up to 100 MHz Up Translation and Greater Than 100 MHz Down Translation at ≤ 30pF Cap Load and Up To 40 MHz Up/Down Translation at 50 pF Cap Load." 1
- Updated all propagation delay tables changed from generic to specific LSF devices. 9

Changes from Revision D (October 2014) to Revision E (July 2015) **Page**

- Deleted "Less Than 1.5 ns Max Propagation Delay" from Features. 1
- Updated ESD Ratings table. 7
- Increased MAX value for T_A, Operating free-air temperature, from 85°C to 125°C..... 7
- Updated the *Device Functional Modes* section..... 14
- Updated the *Pull-Up Resistor Sizing* section..... 18

Changes from Revision C (May 2014) to Revision D (August 2014) **Page**

- Changed bidirectional voltage level translation from 1.0 to 0.95 1
- Changed YZT package to fix view error. 1
- Changed YZT Package, to fix view error. 4
- Added Vref_A footnote..... 17

Changes from Revision B (May 2014) to Revision C (May 2014) **Page**

- Changed LSF0108 status from preview to production..... 1
- Updated document title. 1
- Updated Handling Ratings table. 7

Changes from Revision A (January 2014) to Revision B (February 2014) **Page**

- Added LSF0108 to data sheet. 1

Changes from Revision * (December 2013) to Revision A (January 2014) **Page**

- Updated part number..... 1
- Updated *Electrical Characteristics* table..... 9

5 Pin Configuration and Functions

Pinout drawings are not to scale

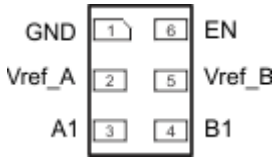


Figure 5-1. LSF0101 DRY Package, 6-Pin SON (Transparent Top View)

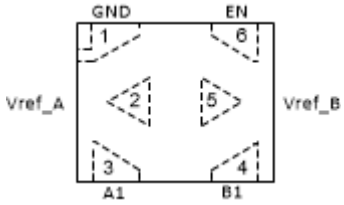


Figure 5-2. LSF0101 DTQ Package, 6-Pin X2SON (Transparent Top View)

Table 5-1. Pin Functions

PIN		TYPE[1]	DESCRIPTION
NAME	DRY, DTQ NO.		
An	3	I/O	Auto-Bidirectional Data port
Bn	4	I/O	
EN	6	I	Enable input; connect to Vref_B and pull-up through a high resistor (200 kΩ). See Using the Enable Pin with the LSF Family
GND	1	—	Ground
Vref_A	2	—	Reference supply voltage. For proper device biasing, see *Section 9* and Understanding the Bias Circuit for the LSF Family.
Vref_B	5	—	

(1) I= input, O = output

Pinout drawings are not to scale

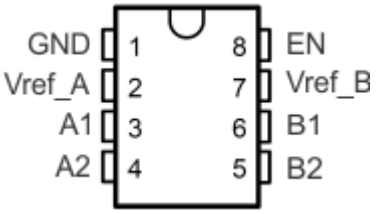


Figure 5-3. LSF0102 DCT, DCU or DDF Package, 8-Pin SM8, VSSOP, SOT-23 (Top View)

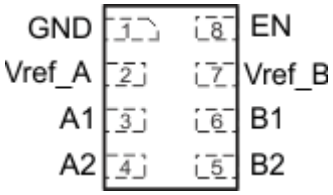


Figure 5-4. LSF0102 DQE Package, 8-Pin X2SON (Transparent Top View)

Table 5-2. Pin Functions

PIN		TYPE[1]	DESCRIPTION
NAME	DCT, DCU, DDF, DQE NO.		
An	3, 4	I/O	Auto-Bidirectional Data port
Bn	6, 5	I/O	
EN	8	I	Enable input; connect to Vref_B and pull-up through a high resistor (200 kΩ). See Using the Enable Pin with the LSF Family
GND	1	—	Ground
Vref_A	2	—	Reference supply voltage. For proper device biasing, see *Section 9* and Understanding the Bias Circuit for the LSF Family.
Vref_B	7	—	

(1) I= input, O = output

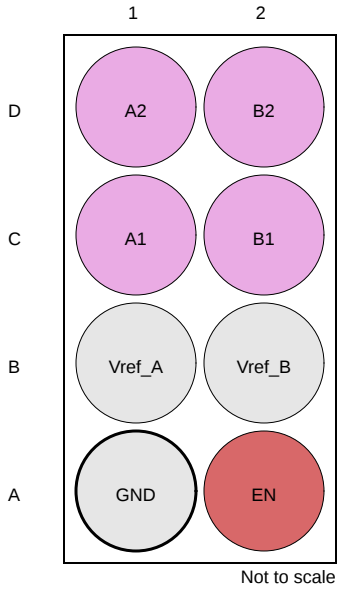


Figure 5-5. LSF0102 YZT Package, 8-Pin DSBGA (Bottom View)

Legend	
Input	Input or Output
Ground	

Table 5-3. Pin Functions

PIN		TYPE(1)	DESCRIPTION
YZT NO.	NAME		
C1	A1	I/O	Auto-Bidirectional Data port
D1	A2	I/O	
C2	B1	I/O	
D2	B2	I/O	
B1	Vref_A	—	Reference supply voltage. For proper device biasing, see *Section 9* and Understanding the Bias Circuit for the LSF Family.
B2	Vref_B	—	
A2	EN	I	Enable input; connect to Vref_B and pull-up through a high resistor (200 kΩ). See Using the Enable Pin with the LSF Family
A1	GND	—	Ground

(1) I= input, O = output

Pinout drawings are not to scale

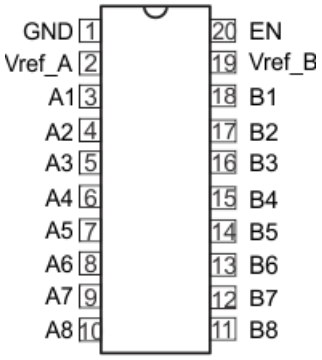


Figure 5-6. LSF0108 PW or DGS Package, 20-Pin TSSOP or VSSOP (Top View)

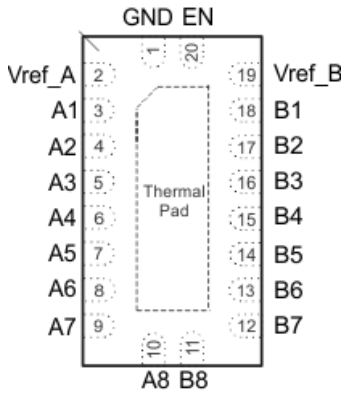


Figure 5-7. LSF0108 RKS Package, 20-Pin VQFN (Transparent Top View)

Table 5-4. Pin Functions

PIN		TYPE(1)	DESCRIPTION
NAME	PW, DGS RKS NO.		
An	3 to 10	I/O	Auto-Bidirectional Data port
Bn	18 to 11	I/O	
EN	20	I	Enable input; connect to Vref_B and pull-up through a high resistor (200 kΩ). See Using the Enable Pin with the LSF Family
GND	1	—	Ground
Vref_A	2	—	Reference supply voltage. For proper device biasing, see *Section 9* and Understanding the Bias Circuit for the LSF Family.
Vref_B	19	—	

(1) I= input, O = output

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_I	Input voltage(2)		–0.5	7	V
$V_{I/O}$	Input/output voltage(2)		–0.5	7	V
	Continuous channel current			128	mA
I_{IK}	Input clamp current	$V_I < 0$		–50	mA
T_J	Junction Temperature			150	°C
T_{stg}	Storage temperature range		–65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input and input/output negative-voltage ratings may be exceeded if the input and input/output clamp-current ratings are observed.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 500-V HBM is possible with the necessary precautions.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 250-V CDM is possible with the necessary precautions.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
$V_{I/O}$	Input/output voltage	0	5	V
$V_{ref\_A/B/EN}$	Reference voltage	0	5	V
I_{PASS}	Pass transistor current		64	mA
T_A	Operating free-air temperature	–40	125	°C

6.4 Thermal Information

THERMAL METRIC(1)		LSF0101		UNIT
		DTQ (X2SON)	DRY (SON)	
		6 PINS	6 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	294.4	407.0	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	188.9	285.2	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	216.8	271.6	°C/W
ψ_{JT}	Junction-to-top characterization parameter	26.5	113.5	°C/W
ψ_{JB}	Junction-to-board characterization parameter	216.0	271.0	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	n/a	n/a	°C/W

6.5 Thermal Information

THERMAL METRIC[1]		LSF0102					UNIT
		DCU (US8)	DCT (SM8)	DQE (X2SON)	YZT (DSBGA)	DDF (SOT-23)	
		8 PINS	8 PINS	8 PINS	8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	210.1	189.6	246.5	125.5	243.3	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	89.1	119.6	149.1	1.0	168.7	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	88.8	102.1	100.0	62.7	157.6	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	8.3	44.5	17.1	3.4	45.9	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	88.4	101.0	99.8	62.7	157.2	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	n/a	n/a	n/a	n/a	n/a	°C/W

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953.

6.6 Thermal Information

THERMAL METRIC[1]		LSF0108			UNIT
		RKS (VQFN)	PW (TSSOP)	DGS (VSSOP)	
		20 PINS	20 PINS	20 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	49.3	106.6	123.0	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	45.9	41.0	62.2	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	20.6	57.6	77.4	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	2.5	4.2	8.8	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	20.6	47.0	77.0	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	3.4	n/a	n/a	°C/W

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953.

6.7 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			MIN	TYP(1)	MAX	UNIT
V_{IK}	I_I = –18 mA,	V_{EN} = 0				–1.2	V
I_{IH}	V_I = 5 V	V_{EN} = 0				5.0	µA
I_{CC}	V_{ref_B} = V_{EN} = 5.5 V, V_{ref_A} = 4.5 V, I_O = 0, V_I = V_{CC} or GND				6		µA
$C_{I(ref\_A/B/EN)}$	V_I = 3 V or 0				11		pF
$C_{io(off)}$	V_O = 3 V or 0,	V_{EN} = 0			4.0	6.0	pF
$C_{io(on)}$	V_O = 3 V or 0,	V_{EN} = 3 V			10.5	12.5	pF
r_{on} (2)	V_I = 0,	I_O = 64 mA	V_{ref_A} = 3.3 V; V_{ref_B} = V_{EN} = 5 V		8.0		Ω
			V_{ref_A} = 1.8 V; V_{ref_B} = V_{EN} = 5 V		9.0		
			V_{ref_A} = 1.0 V; V_{ref_B} = V_{EN} = 5 V		10		
	V_I = 0,	I_O = 32 mA	V_{ref_A} = 1.8 V; V_{ref_B} = V_{EN} = 5 V		10		Ω
			V_{ref_A} = 2.5 V; V_{ref_B} = V_{EN} = 5 V		15		
	V_I = 1.8 V,	I_O = 15 mA	V_{ref_A} = 3.3 V; V_{ref_B} = V_{EN} = 5 V		9.0		Ω
	V_I = 1.0 V,	I_O = 10 mA	V_{ref_A} = 1.8 V; V_{ref_B} = V_{EN} = 3.3 V		18		Ω
	V_I = 0 V,	I_O = 10 mA	V_{ref_A} = 1.0 V; V_{ref_B} = V_{EN} = 3.3 V		20		Ω
	V_I = 0 V,	I_O = 10 mA	V_{ref_A} = 1.0 V; V_{ref_B} = V_{EN} = 1.8 V		30		Ω

(1) All typical values are at T_A = 25°C.
(2) Measured by the voltage drop between the A and B pins at the indicated current through the switch. On-state resistance is determined by the lowest voltage of the two (A or B) pins.

6.8 LSF0101/02 AC Performance (Translating Down) Switching Characteristics , V_{GATE} = 3.3 V

over recommended operating free-air temperature range, V_{GATE} = 3.3 V, V_{IH} = 3.3 V, V_{IL} = 0, and V_M = 1.15 V (unless otherwise noted) (see Figure 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	C_L = 50 pF		C_L = 30 pF		C_L = 15 pF		UNIT
			TYP	MAX	TYP	MAX	TYP	MAX	
t_{PLH}	A or B	B or A	1.1		0.7		0.3		ns
t_{PHL}			1.2		0.8		0.4		

6.9 LSF0108 AC Performance (Translating Down) Switching Characteristics, V_{GATE} = 3.3 V

over recommended operating free-air temperature range, V_{GATE} = 3.3 V, V_{IH} = 3.3 V, V_{IL} = 0, and V_M = 1.15 V (unless otherwise noted) (see Figure 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	C_L = 50 pF		C_L = 30 pF		C_L = 15 pF		UNIT
			TYP	MAX	TYP	MAX	TYP	MAX	
t_{PLH}	A or B	B or A	1.9		1.4		0.75		ns
t_{PHL}			2		1.5		0.85		

6.10 LSF0101/02 AC Performance (Translating Down) Switching Characteristics, V_{GATE} = 2.5 V

over recommended operating free-air temperature range, V_{GATE} = 2.5 V, V_{IH} = 2.5 V, V_{IL} = 0, and V_M = 0.75 V (unless otherwise noted) (see Figure 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	C_L = 50 pF		C_L = 30 pF		C_L = 15 pF		UNIT
			TYP	MAX	TYP	MAX	TYP	MAX	
t_{PLH}	A or B	B or A	1.2		0.8		0.35		ns
t_{PHL}			1.3		1		0.5		

6.11 LSF0108 AC Performance (Translating Down) Switching Characteristics, V_{GATE} = 2.5 V

over recommended operating free-air temperature range, V_{GATE} = 2.5 V, V_{IH} = 2.5 V, V_{IL} = 0, and V_M = 0.75 V (unless otherwise noted) (see Figure 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	C_L = 50 pF		C_L = 30 pF		C_L = 15 pF		UNIT
			TYP	MAX	TYP	MAX	TYP	MAX	
t_{PLH}	A or B	B or A	2		1.45		0.8		ns
t_{PHL}			2.1		1.55		0.9		

6.12 LSF0101/02 AC Performance (Translating Up) Switching Characteristics, V_{GATE} = 3.3 V

over recommended operating free-air temperature range, V_{GATE} = 3.3 V, V_{IH} = 2.3 V, V_{IL} = 0, V_T = 3.3 V, V_M = 1.15 V and R_L = 300 (unless otherwise noted) (see Figure 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	C_L = 50 pF		C_L = 30 pF		C_L = 15 pF		UNIT
			TYP	MAX	TYP	MAX	TYP	MAX	
t_{PLH}	A or B	B or A	1		0.8		0.4		ns
t_{PHL}			1		0.9		0.4		

6.13 LSF0108 AC Performance (Translating Up) Switching Characteristics, V_{GATE} = 3.3 V

over recommended operating free-air temperature range, V_{GATE} = 3.3 V, V_{IH} = 2.3 V, V_{IL} = 0, V_T = 3.3 V, V_M = 1.15 V and R_L = 300 (unless otherwise noted) (see Figure 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	C_L = 50 pF		C_L = 30 pF		C_L = 15 pF		UNIT
			TYP	MAX	TYP	MAX	TYP	MAX	
t_{PLH}	A or B	B or A	2.1		1.55		0.9		ns
t_{PHL}			2.2		1.65		1		

6.14 LSF0101/02 AC Performance (Translating Up) Switching Characteristics, V_{GATE} = 2.5 V

over recommended operating free-air temperature range, V_{GATE} = 2.5 V, V_{IH} = 1.5 V, V_{IL} = 0, V_T = 2.5 V, V_M = 0.75 V and R_L = 300 (unless otherwise noted) (see Figure 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	C_L = 50 pF		C_L = 30 pF		C_L = 15 pF		UNIT
			TYP	MAX	TYP	MAX	TYP	MAX	
t_{PLH}	A or B	B or A	1.1		0.9		0.45		ns
t_{PHL}			1.3		1.1		0.6		

6.15 LSF0108 AC Performance (Translating Up) Switching Characteristics, V_{GATE} = 2.5 V

over recommended operating free-air temperature range, V_{GATE} = 2.5 V, V_{IH} = 1.5 V, V_{IL} = 0, V_T = 2.5 V, V_M = 0.75 V and R_L = 300 (unless otherwise noted) (see Figure 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	C_L = 50 pF		C_L = 30 pF		C_L = 15 pF		UNIT
			TYP	MAX	TYP	MAX	TYP	MAX	
t_{PLH}	A or B	B or A	1.8		1.35		0.8		ns
t_{PHL}			1.9		1.45		0.9		

6.16 Typical Characteristics

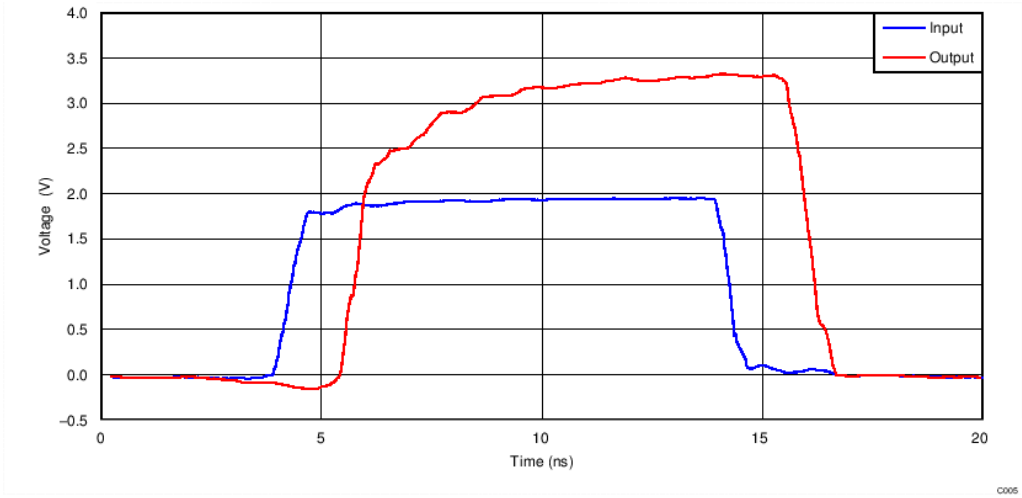
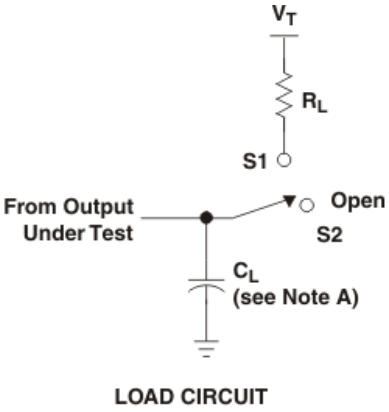


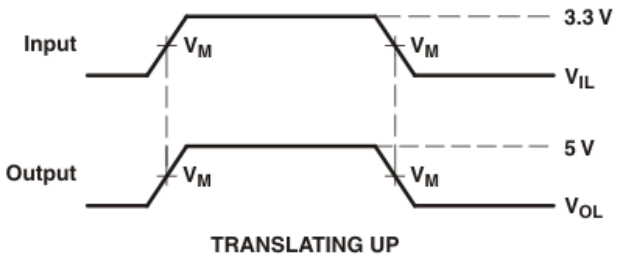
Figure 6-1. Signal Integrity (1.8 to 3.3 V Up Translation at 50 MHz)

7 Parameter Measurement Information

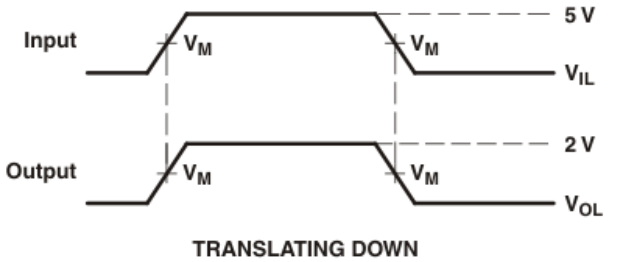


LOAD CIRCUIT

USAGE	SWITCH
Translating up	S1
Translating down	S2



TRANSLATING UP



TRANSLATING DOWN

NOTES: A. C_L includes probe and jig capacitance.
B. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
C. The outputs are measured one at a time, with one transition per measurement.

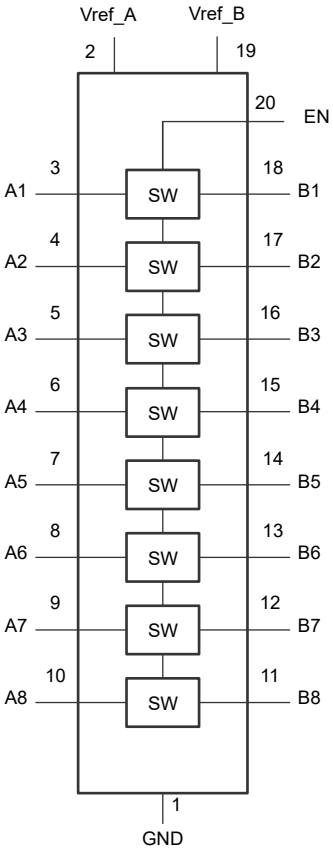
Figure 7-1. Load Circuit for Outputs

8 Detailed Description

8.1 Overview

The LSF family can be used in level-translation applications for interfacing devices or systems operating with one another that operate at different interface voltages. The LSF family is ideal for use in applications where an open-drain driver is connected to the data I/Os. With appropriate pull-up resistors and layout, LSF can achieve 100 MHz. The LSF family can also be used in applications where a push-pull driver is connected to the data I/Os. For an overview of device setup and operation, see *The Logic Minute* training series on *Understanding the LSF Family of Bidirectional, Multi-Voltage Level Translators*.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Auto Bidirectional Voltage Translation

All devices in the LSF family are auto bidirectional voltage level translators that are operational from 0.95 to 4.5 V on the Vref_A supply and from 1.8 to 5.5 V on the Vref_B supply. This allows bidirectional voltage translation between 0.95 V and 5.5 V without the need for a direction pin in open-drain or push-pull applications. The LSF family supports level translation applications with transmission speeds greater than 100 Mbps for open-drain systems using a 30-pF capacitance and 250-Ω pullup resistor. Both the output driver of the controller and the peripheral device output can be push-pull or open-drain (pull-up resistors may be required). In both up and down translation, the B-side is often referred to as the high side and refers to devices connected to the B ports. The A-side can be referred to as the low side.

8.3.2 Output Enable

To enable the I/O pins, the EN input should be tied directly to Vref_B during operation and both pins must be pulled up to the HIGH side (Vpu or VCCB) through a pull-up resistor (typically 200 kΩ). To ensure the high impedance state during power-up, power-down, or during operation, the EN pin must be LOW. The EN pin should always be tied directly to the Vref_B pin and is recommended to be disabled by an open-drain driver without a pullup resistor. This allows Vref_B to regulate the EN input and bias the channels for proper translation. A filter capacitor on Vref_B is recommended for a stable supply at the device.

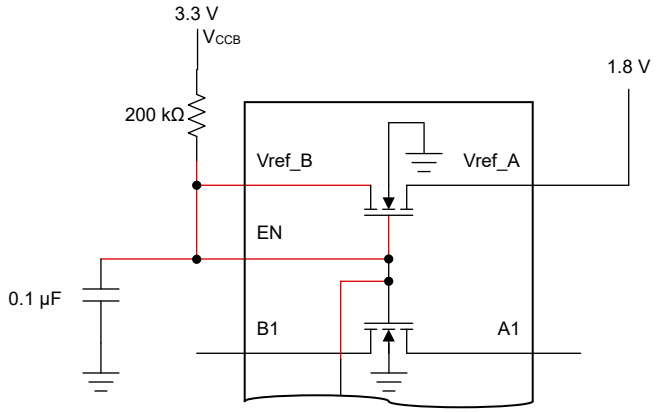


Figure 8-1. Enable Pin Tied to Vref_B Directly and to VCCB Through a Pull-Up Resistor

The supply voltage of open drain I/O devices can be completely different from the supplies used for the LSF and has no impact on the operation. For additional details on how to use the enable pin, see the *Using the Enable Pin with the LSF Family video.*

Table 8-1. Enable Pin Function Table

INPUT EN(1) PIN	Data Port State
Tied directly to Vref_B	An = Bn
L	Hi-Z

(1) EN is controlled by V_{ref_B} logic levels.

8.4 Device Functional Modes

For each channel (n), when either the An or Bn port is LOW, the switch provides a low impedance path between the An and Bn ports; the corresponding Bn or An port will be pulled LOW. The low R_{ON} of the switch allows connections to be made with minimal propagation delay and signal distortion.

Table 8-1 provides a summary of device operation. For additional details on the functional operation of the LSF family of devices, see the *Down Translation with the LSF Family* and *Up Translation with the LSF Family* videos.

Table 8-2. Device Functionality

Signal Direction(1)	Input State	Switch State	Functionality
B to A (Down Translation)	B = LOW	ON (Low Impedance)	A-side voltage is pulled low through the switch to the B-side voltage
	B = HIGH	OFF (High Impedance)	A-side voltage is clamped at Vref_A (2)
A to B (Up Translation)	A = LOW	ON (Low Impedance)	B-side voltage is pulled low through the switch to the A-side voltage
	A = HIGH	OFF (High Impedance)	B-side voltage is clamped at Vref_A and then pulled up to the Vpu# supply voltage

(1) The downstream channel should not be actively driven through a low impedance driver, or else bus contention may occur.
(2) The A-side can have a pullup to Vref_A for additional current drive capability or may also be pulled above Vref_A with a pullup resistor. Specifications in the *Recommended Operating Conditions* section should always be followed.

8.4.1 Up and Down Translation

Up Translation:

When the signal is being driven from A to B and the An port is HIGH, the switch will be OFF and the Bn port will then be driven to a voltage higher than Vref_A by the pullup resistor that is connected to the pull-up supply voltage (Vpu#). This functionality allows seamless translation between higher and lower voltages selected by the user, without the need for directional control. Pull-up resistors are always required on the high side, and pull-ups are only required on the low side if the low side device's output is open drain or its input has a leakage greater than 1 µA.

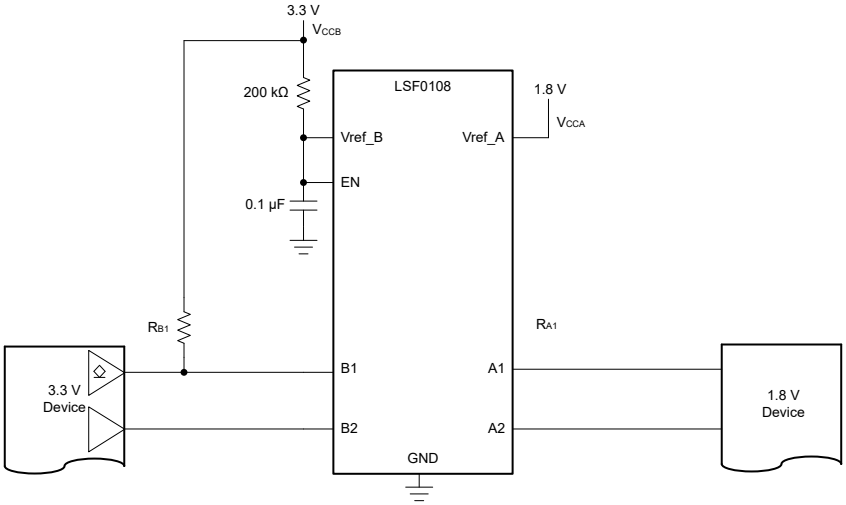


Figure 8-2. Up Translation Example Schematic with Push-Pull and Open Drain Configuration

Up translation with the LSF requires attention to two important factors: maximum data rate and sink current. Maximum data rate is directly related to the rising edge of the output signal. Sink current depends on supply values and the chosen pull-up resistor values. Equation 1 below shows the maximum data rate formula and equation 2 presents the maximum sink current formula, both of which are estimations. A low RC value is needed to reach high speeds, which also require strong drivers. Please see the *Up Translation with the LSF Family* video for estimated data rate and sink current calculations based on circuit components.

Down Translation:

$$\frac{1}{3 \times 2R_{B1}C_{B1}} = \frac{1}{6R_{B1}C_{B1}}\left(\frac{bits}{second}\right) \quad (1)$$

$$I_{OL} \cong \frac{V_{CCA}}{R_{A1}} + \frac{V_{CCB}}{R_{B1}}\left(A\right) \quad (2)$$

When the signal is being driven HIGH from the Bn port to An port, the switch will be OFF, clamping the voltage on the An port to the voltage set by Vref_A. A pull-up resistor can be added on either side of the device. There are special circumstances that allow the removal of one or both of the pull-up resistors. If the signal is always going to be down translated from a push-pull transmitter, then the resistor on the B-side can be removed. If the leakage current into the receiver on the A-side is less than 1 µA, then the resistor on the A-side can also be removed. This arrangement with no external pull-up resistors can be used when down translating from a push-pull output to a low-leakage input. For an open drain transmitter, the pull-up resistor on the B-side is necessary because an open drain output can't drive high by itself. Refer to Table 8-2 for a summary of device operation. For additional details on the functional operation of the LSF family of devices, see the *Up Translation with the LSF Family* and *Down Translation with the LSF Family* videos.

9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

The LSF devices are able to perform voltage translation for open-drain or push-pull interfaces. Table 9-1 provides common interfaces and the corresponding device recommendation from the LSF family which supports the corresponding bit count.

Table 9-1. Voltage Translator for Common Interfaces

Part Name	Channel Number	Interface
LSF0101	1	GPIO
LSF0102	2	GPIO, MDIO, SMBus, PMBus, and I^2C
LSF0108	8	GPIO, MDIO, SDIO, SVID, UART, SMBus, PMBus, I^2C, and SPI

Please find below some important reminders regarding the LSF family of devices:

- LSF devices are switch-based, not buffer-based (please see the TXB family for buffer-based devices).
- Specific data rates cannot be calculated by using 1/Tpd.
- VCCB/VCCA are not the same as Vref_B or Vref_A: VCCB refers to the B-side supply voltage supplied to the LSF device, while Vref_B refers to the voltage at the Vref_B pin (pin 7 of Figure 9-1.) on the other side of the 200k resistor.

9.2 Typical Applications

9.2.1 Open-Drain Interface (I^2C, PMBus, SMBus, and GPIO)

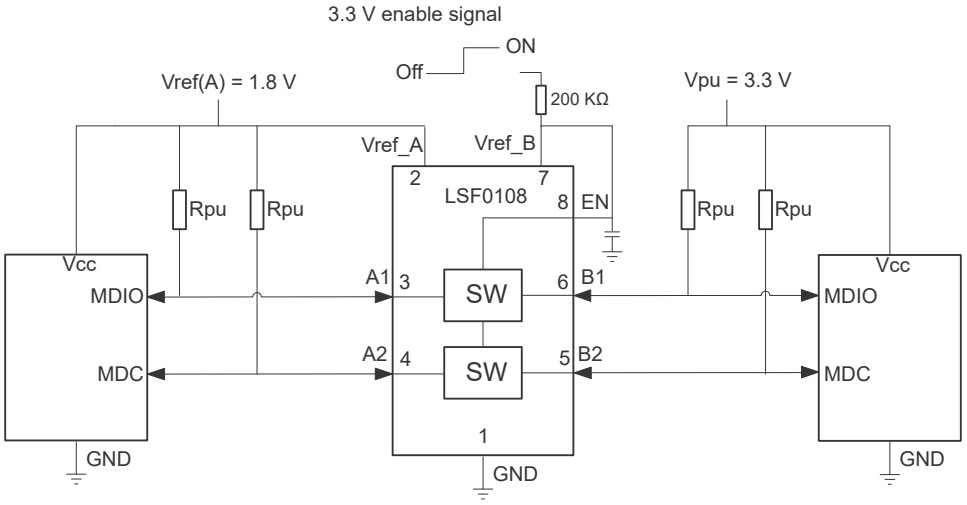


Figure 9-1. Typical Application Circuit for Open-Drain Translation (MDIO Shown as an Example)

9.2.1.1 Design Requirements

9.2.1.1.1 Enable, Disable, and Reference Voltage Guidelines

When Vref_B is connected through a 200-kΩ resistor to a 3.3-V Vpu power supply and Vref_A is set 1.8 V, as shown in Figure 9-1, the A1 and A2 channels have a maximum output voltage equal to Vref_A, and the B1 and B2 channels have has a maximum output voltage equal to Vpu.

The LSF family has an EN input that is used to disable the device by setting EN LOW, placing all I/Os in the high-impedance state. Since the LSF family of devices are switch-type voltage translators, the power consumption is very low. TI recommends always enabling the LSF family for bidirectional applications (I^2C, SMBus, PMBus, or MDIO).

Table 9-2. Application Operating Condition

PARAMETER		MIN	TYP	MAX	UNIT
Vref_A(1)	reference voltage (A)	0.95		5.0	V
Vref_B	reference voltage (B)	Vref_A + 0.8		5.0	V
$V_{I(EN)}$	input voltage on EN pin	Vref_A + 0.8		5.0	V
Vpu	pull-up supply voltage	0		Vref_B	V

(1) Vref_A is required to be the lowest voltage level across all inputs and outputs.

Note

The 200 kΩ, pull-up resistor is required to allow Vref_B to regulate the EN input and properly bias the device for translation.

9.2.1.1.2 Bias Circuitry

For proper operation, VCCA must always be at least 0.8 V less than VCCB (VCCA + 0.8 ≦ VCCB). The 200 kΩ pull-up resistor is required to allow Vref_B to regulate the EN input and properly bias the device for translation. A 0.1 µF capacitor is recommended for providing a path from Vref_B to ground for high frequency noise. Vref_B and VI (EN) are recommended to be 1.0 V higher than Vref_A for best signal integrity.

Attempting to drive the EN pin directly with a push-pull output device is a very common design error with the LSF01 series of devices. It is also very important to note that current does flow into the A-side voltage supply during normal operation. Not all voltage sources can sink current, so be sure that applicable designs can handle this current. For more design details, see the *Understanding the Bias Circuit for the LSF Family* video.

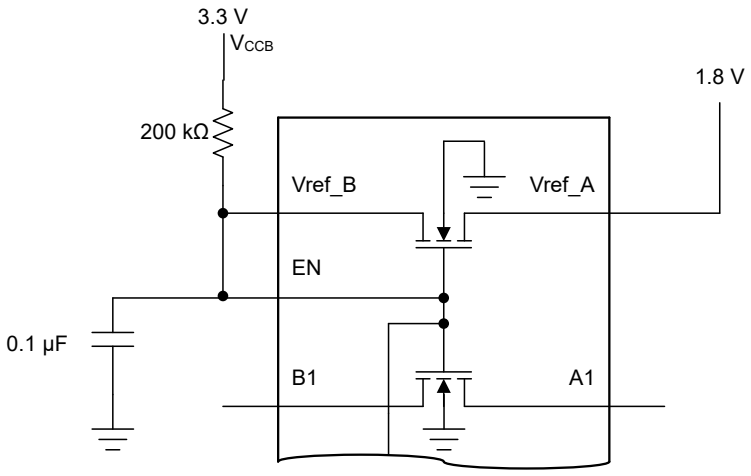


Figure 9-2. Bias Circuitry Inside the LSF0108 Devices

9.2.1.2 Detailed Design Procedure

9.2.1.2.1 Bidirectional Translation

For the bidirectional translation configuration (higher voltage to lower voltage or lower voltage to higher voltage), the EN input must be connected to Vref_B and both pins must be pulled up to the HIGH side Vpu through a pull-up resistor (typically 200 kΩ). This allows Vref_B to regulate the EN input and bias the channels for proper translation. A filter capacitor on Vref_B is recommended for a stable supply at the device. The controller output driver can be push-pull or open-drain (pull-up resistors may be required) and the peripheral device output can be push-pull or open-drain (pull-up resistors are required to pull the Bn outputs to Vpu).

Note

If either output is push-pull, data must be unidirectional or the outputs must be tri-state and be controlled by some direction-control mechanism to prevent HIGH-to-LOW bus contention in either direction. If both outputs are open-drain, no direction control is needed.

9.2.1.2.2 Pull-Up Resistor Sizing

The pull-up resistor value needs to limit the current through the pass transistor when it is in the ON state to about 15 mA. This ensures a voltage drop of 260 mV to 350 mV to have a valid LOW signal on the downstream channel. If the current through the pass transistor is higher than 15 mA, the voltage drop is also higher in the ON state. To set the current through each pass transistor at 15 mA, calculate the pull-up resistor value using the following equation:

$$Rpu = \frac{(\text{Vpu} - 0.35\ \text{V})}{0.015\ A} \quad (3)$$

Table 9-3 summarizes resistor values, reference voltages, and currents at 8 mA, 5 mA, and 3 mA. The resistor value shown in the +10% column (or a larger value) should be used to ensure that the voltage drop across the transistor is 350 mV or less. The external driver must be able to sink the total current from the resistors on both sides of the LSF family device at 0.175 V, although the 15 mA applies only to current flowing through the LSF family device. The device driving the low state at 0.175 V must sink current from one or more of the pull-up resistors and maintain VOL. A decrease in resistance will increase current, and thus result in increased VOL.

Table 9-3. Pull-Up Resistor Values

V_{DPU} (1) (2)	8 mA		5 mA		3 mA	
	NOMINAL (Ω)	+10%(3) (Ω)	NOMINAL (Ω)	+10%(3) (Ω)	NOMINAL (Ω)	+10%(3) (Ω)
5 V	581	639	930	1023	1550	1705
3.3 V	369	406	590	649	983	1082
2.5 V	269	296	430	473	717	788
1.8 V	181	199	290	319	483	532
1.5 V	144	158	230	253	383	422
1.2 V	106	117	170	187	283	312

(1) Calculated for V_{OL} = 0.35 V
(2) Assumes output driver V_{OL} = 0.175 V at stated current
(3) +10% to compensate for V_{DD} range and resistor tolerance

9.2.1.3 Application Curve

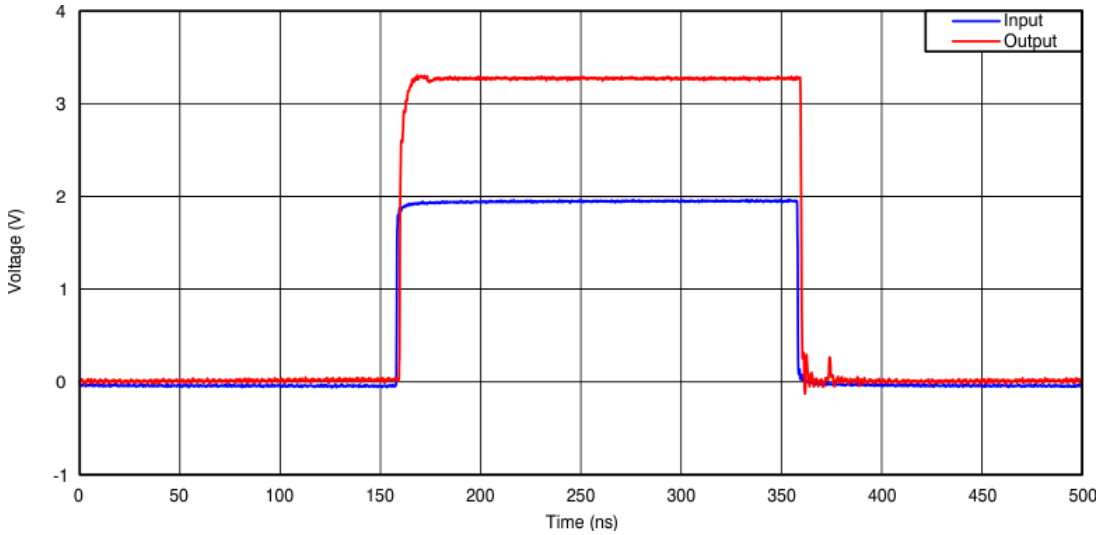


Figure 9-3. Open Drain Translation (1.8 V to 3.3 V at 2.5 MHz)

9.2.2 Mixed-Mode Voltage Translation

The supply voltage ($V_{pu\#}$) for each channel can be individually set with a pull-up resistor. Figure 9-4 shows an example of this mixed-mode multi-voltage translation. For additional details on multi-voltage translation, see the *Multi-voltage Translation with the LSF Family* video.

With the Vref_B pulled up to 5 V and Vref_A connected to 1.8 V, all channels will be clamped to 1.8 V at which point a pullup can be used to define the high level voltage for a given channel.

- **Push-Pull Down Translation (5 V to 1.8 V):** Channel 1 is an example of this setup. When B1 is 5 V, A1 is clamped to 1.8 V, and when B1 is LOW, A1 is driven LOW through the switch.
- **Push-Pull Up Translation (1.8 V to 5 V)**: Channel 2 is an example of this setup. When A2 is 1.8 V, the switch is high impedance and the B2 channel is pulled up to 5 V. When A2 is LOW, B2 is driven LOW through the switch.
- **Push-Pull Down Translation (3.3 V to 1.8 V):** Channels 3 and 4 are examples of this setup. When either B3 or B4 are driven to 3.3 V, A3 or A4 are clamped to 1.8 V, and when either B3 or B4 are LOW, A3 or A4 are driven LOW through the switch.
- **Open-Drain Bidirectional Translation (3.3 V ↔ 1.8 V):** Channels 5 through 8 are examples of this setup. These channels are for bidirectional operation for I^2C and MDIO to translate between 1.8 V and 3.3 V with open-drain drivers.

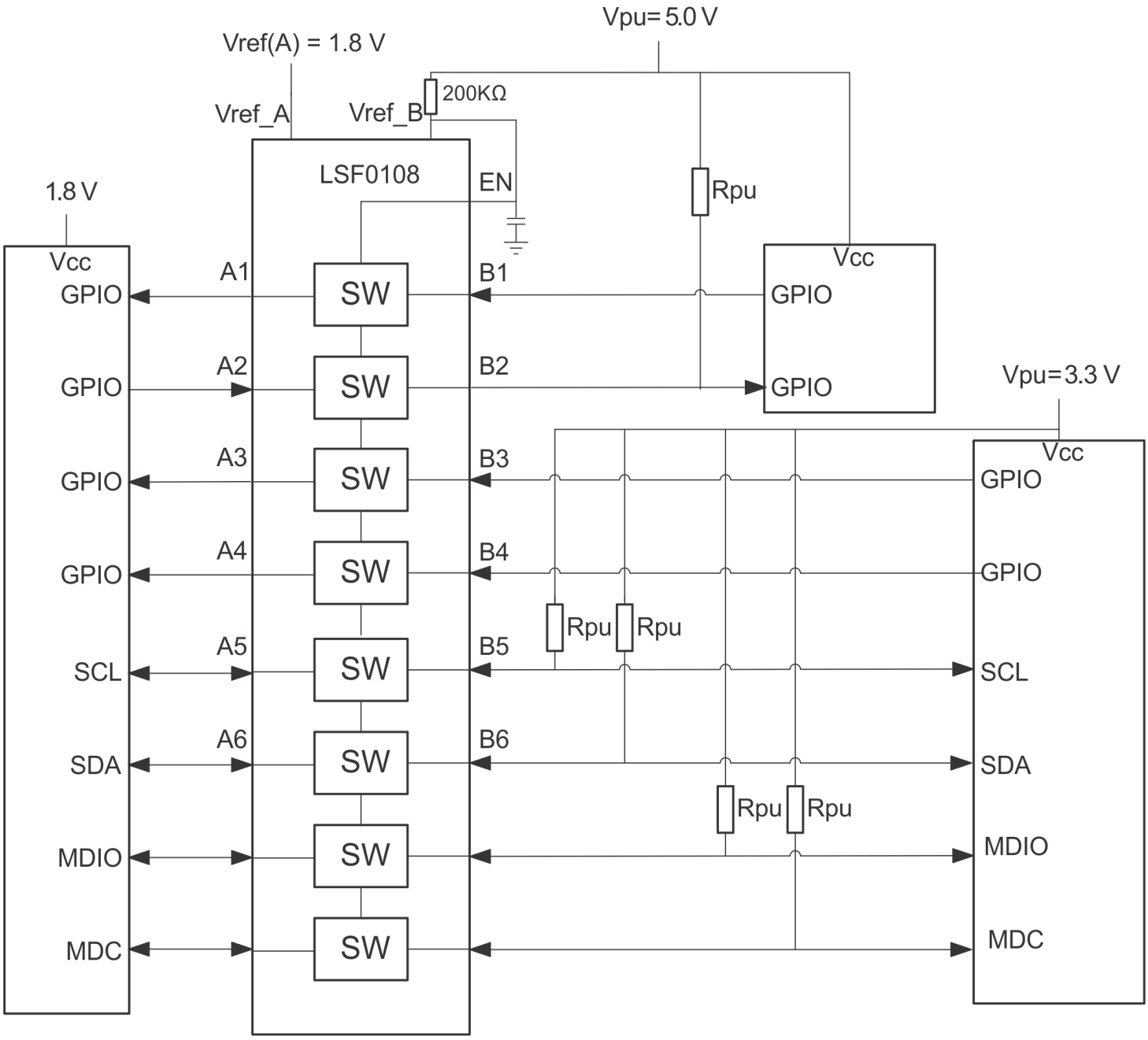


Figure 9-4. Multi-Voltage Translation with the LSF0108

9.2.3 Single Supply Translation

Sometimes, an external device will have an unknown voltage that could be above or below the desired translation voltage, preventing a normal connection of the LSF. Resistors are added on the A side in place of the second supply in this case – this is an example of when LSF single supply operation is utilized, shown in Figure 9-5. In the following figure, a single 3.3 V supply is used to translate between a 3.3 V device and a device that can change between 1.8 V and 5.0 V. R1 and R2 are added in place of the second supply. Note that due to some current coming out of the Vref_A pin, this cannot be treated as a simple voltage divider.

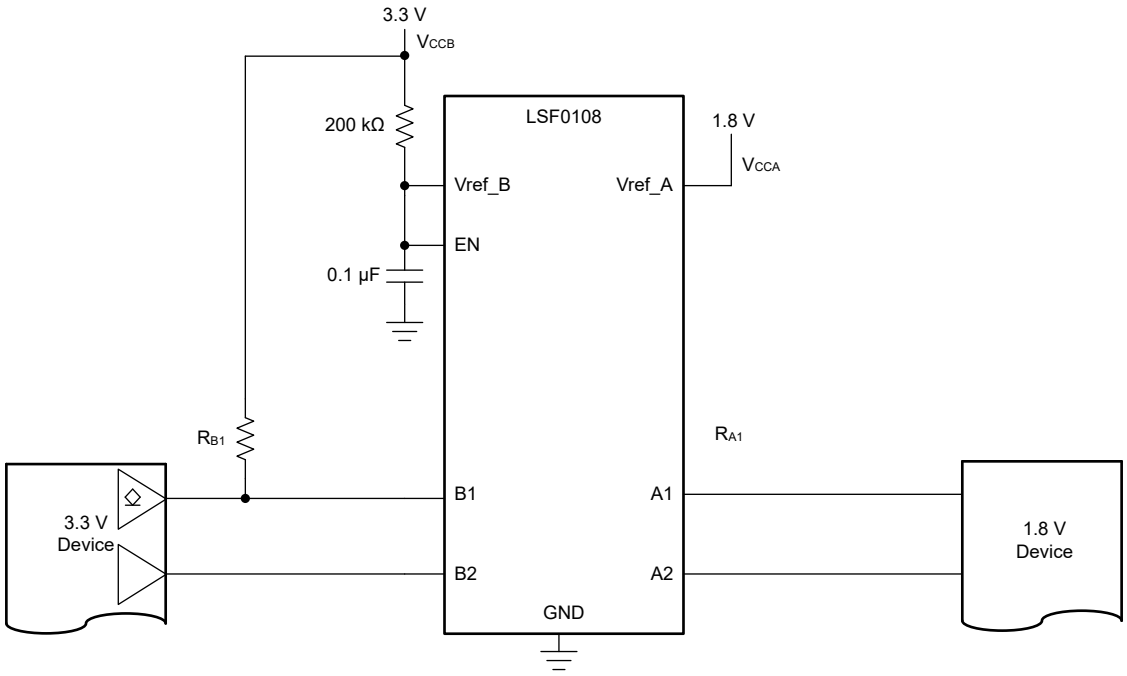


Figure 9-5. Single Supply Translation with 3.3 V Supply

The steps to select the resistor values for R1 and R2 are as follows:

1. Select a value for R1. Typically, 1 MΩ is used to reduce current consumption.
2. Plug in values for your system into the the following equation. Note that Vref_A is the lowest voltage in the system. VCCB is the primary supply and R1 is the selected value from step 1.

$$R_2 = \frac{200\left(10^3\right) \times R_1 \times V_{REFA}}{\left(200\left(10^3\right) + R_1\right)\left(V_{CCB} - V_{REFA}\right) - 0.85 \times R_1} \quad (4)$$

The single supply used must be at least 0.8 V larger than the lowest desired translation voltage. The voltage at Vref_A must be selected as the lowest voltage to be used in the system. The LSF evaluation module (LSF-EVM) contains unpopulated pads to place R1 and R2 for single supply operation testing. For an example single supply translation schematic and details, see the *Single Supply Translation with the LSF Family* video.

9.2.4 Voltage Translation for Vref_B < Vref_A + 0.8 V

As described in the *Enable, Disable, and Reference Voltage Guidelines* section, it is generally recommended that Vref_B > Vref_A + 0.8 V; however, the device can still operate in the condition where Vref_B < Vref_A + 0.8 V as long as additional considerations are made for the design.

Typical Operation (Vref_B > Vref_A + 0.8 V): in this scenario, pullup resistors are not required on the A-side for proper down-translation as is shown for channels 1 and 2 of Figure 9-4. The typical operating mode of the device ensures that when down translating from B to A, the A-side I/O ports will clamp at Vref_A to provide proper voltage translation. For further explanation of device operation, see the *Down Translation with the LSF Family* video.

Requirements for Vref_B < Vref_A + 0.8 V Operation: in this scenario, there is not a large enough voltage difference between Vref_A and Vref_B to ensure that the A side I/O ports will be clamped at Vref_A, but rather at a voltage approximately equal to Vref_B – 0.8 V. For example, if Vref_B = 1.8 V and Vref_A = 1.2 V, the A-side I/Os will clamp to a voltage around 1.0 V. Therefore, to operate in such a condition, the following additional design considerations must be met:

- Vref_B must be greater than Vref_A during operation (Vref_B > Vref_A)
- Pullup resistors should be populated on A-side I/O ports to ensure the line will be fully pulled up to the desired voltage

Figure 9-6 shows an example of this setup, where 1.2 V ↔ 1.8 V translation is achieved with the LSF0108. This type of setup also applies for other voltage nodes such as 1.8 V ↔ 2.5 V, 1.05 V ↔ 1.5 V, and others as long as the *Recommended Operating Conditions* table is followed.

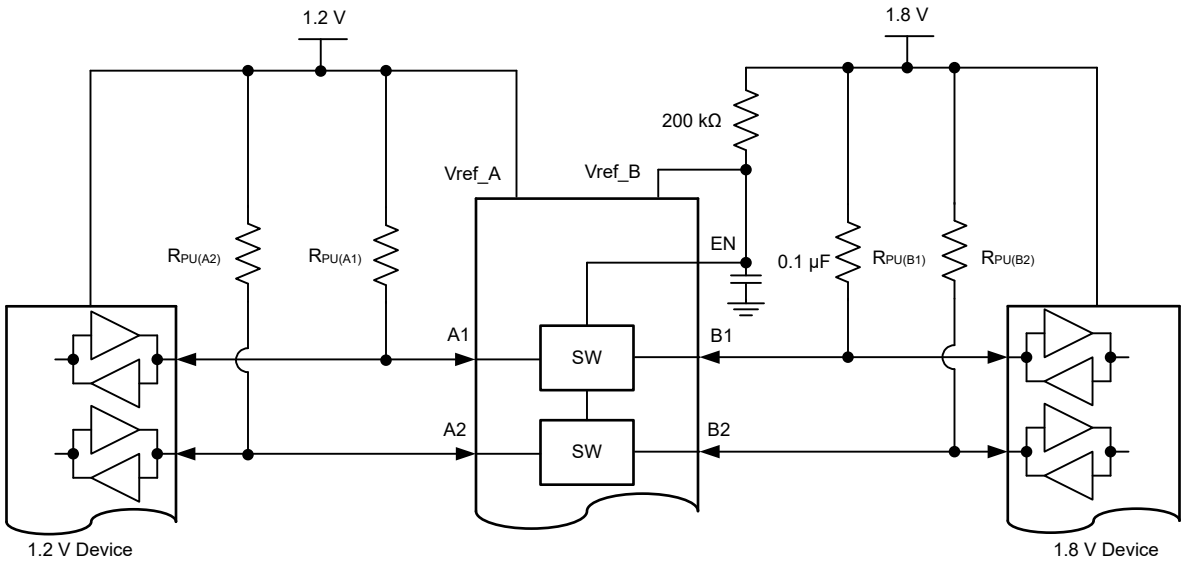


Figure 9-6. 1.2 V to 1.8 V Level Translation with LSF0108

10 Power Supply Recommendations

There are no power sequence requirements for the LSF family. Table 10-1 provides recommended operating voltages for all supply and input pins.

Table 10-1. Recommended Operating Voltages

PARAMETER		MIN	TYP	MAX	UNIT
Vref_A(1)	reference voltage (A)	0.95		5.0	V
Vref_B	reference voltage (B)	Vref_A + 0.8		5.0	V
$V_{I(EN)}$	input voltage on EN pin	Vref_A + 0.8		5.0	V
Vpu	pull-up supply voltage	0		Vref_B	V

(1) Vref_A is required to be the lowest voltage level across all inputs and outputs.

11 Layout

11.1 Layout Guidelines

Because the LSF family is a switch-type level translator, the signal integrity is highly related with a pull-up resistor and PCB capacitance condition.

- Short signal trace as possible to reduce capacitance and minimize stub from pull-up resistor.
- Place LSF close to high voltage side.
- Select the appropriate pull-up resistor that applies to translation levels and driving capability of transmitter.

11.2 Layout Example

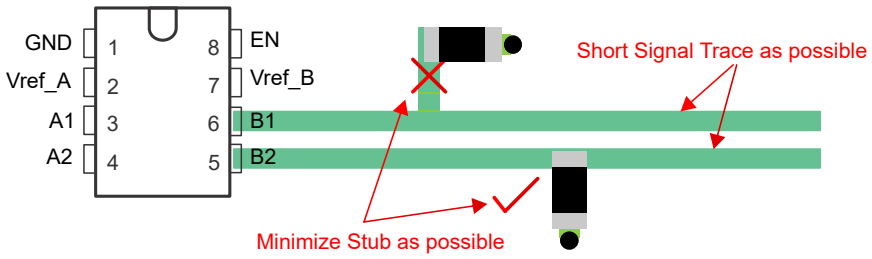


Figure 11-1. Short Trace Layout

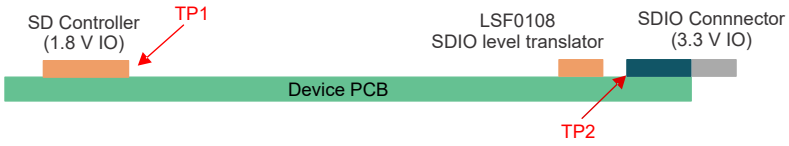


Figure 11-2. Device Placement

12 Device and Documentation Support

12.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, *LSF Translator Family Evaluation Module* user's guide
- Texas Instruments, *Biasing Requirements for TXS, TXB, and LSF Auto-Bidirectional Translators* application note
- Texas Instruments, *Voltage Level Translation with the LSF Family* application note
- The Logic Minute Video Training Series on Understanding the LSF Family of Devices:
  - Texas Instruments, *Introduction - Voltage Level Translation with the LSF Family*
  - Texas Instruments, *Understanding the Bias Circuit for the LSF Family*
  - Texas Instruments, *Using the Enable Pin with the LSF Family*
  - Texas Instruments, *Translation Basics with the LSF Family*
  - Texas Instruments, *Down Translation with the LSF Family*
  - Texas Instruments, *Up Translation with the LSF Family*
  - Texas Instruments, *Multi-Voltage Translation with the LSF Family*
  - Texas Instruments, *Single Supply Translation with the LSF Family*

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 Support Resources

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12.5 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.6 Glossary

TI Glossary	This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LSF0101DRYR	ACTIVE	SON	DRY	6	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	VD	Samples
LSF0101DTQR	ACTIVE	X2SON	DTQ	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	FC	Samples
LSF0102DCTR	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	NG2 (S, Y)	Samples
LSF0102DCUR	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 125	(G2, NG2J, NG2P, NG2S) NY	Samples
LSF0102DQER	ACTIVE	X2SON	DQE	8	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	RV	Samples
LSF0102YZTR	ACTIVE	DSBGA	YZT	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 125	RV	Samples
LSF0108DGSR	ACTIVE	VSSOP	DGS	20	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LSF08	Samples
LSF0108PWR	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	LSF0108	Samples
LSF0108RKSR	ACTIVE	VQFN	RKS	20	3000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	LSF0108	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

OTHER QUALIFIED VERSIONS OF LSF0102, LSF0108 :

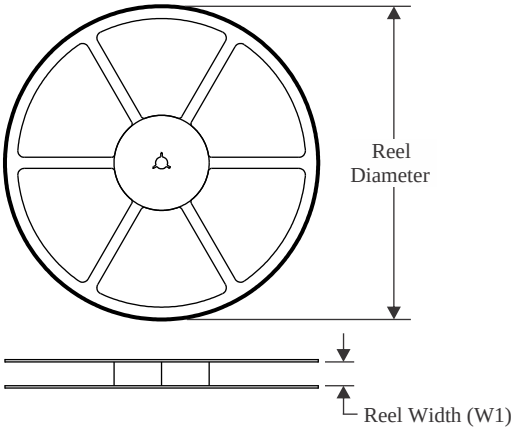
- Automotive : LSF0102-Q1, LSF0108-Q1

NOTE: Qualified Version Definitions:

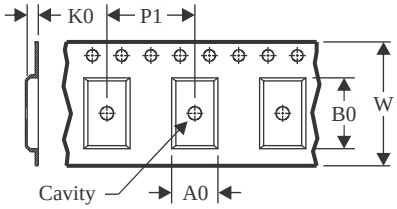
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION

REEL DIMENSIONS

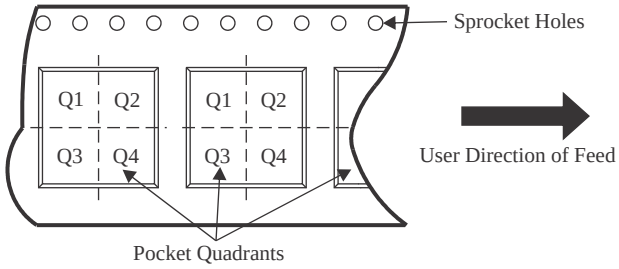


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

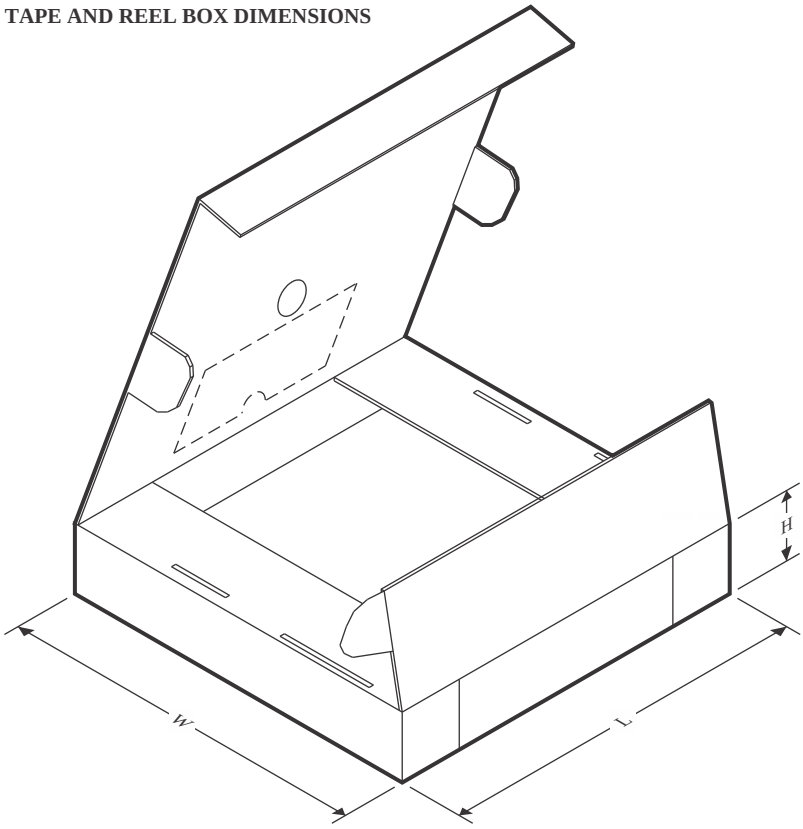
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LSF0101DRYR	SON	DRY	6	5000	180.0	9.5	1.15	1.6	0.75	4.0	8.0	Q1
LSF0101DTQR	X2SON	DTQ	6	3000	180.0	9.5	0.94	1.13	0.5	2.0	8.0	Q2
LSF0102DCTR	SM8	DCT	8	3000	177.8	12.4	3.45	4.4	1.45	4.0	12.0	Q3
LSF0102DCTR	SM8	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
LSF0102DCUR	VSSOP	DCU	8	3000	180.0	9.0	2.25	3.4	1.0	4.0	8.0	Q3
LSF0102DCUR	VSSOP	DCU	8	3000	178.0	9.0	2.25	3.35	1.05	4.0	8.0	Q3
LSF0102DCUR	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
LSF0102DQER	X2SON	DQE	8	5000	180.0	9.5	1.15	1.6	0.5	4.0	8.0	Q1
LSF0102YZTR	DSBGA	YZT	8	3000	180.0	8.4	1.02	2.02	0.75	4.0	8.0	Q1
LSF0108DGSR	VSSOP	DGS	20	5000	330.0	16.4	5.4	5.4	1.45	8.0	16.0	Q1
LSF0108PWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1
LSF0108RKSR	VQFN	RKS	20	3000	177.8	12.4	2.73	4.85	1.03	4.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LSF0101DRYR	SON	DRY	6	5000	184.0	184.0	19.0
LSF0101DTQR	X2SON	DTQ	6	3000	189.0	185.0	36.0
LSF0102DCTR	SM8	DCT	8	3000	183.0	183.0	20.0
LSF0102DCTR	SM8	DCT	8	3000	182.0	182.0	20.0
LSF0102DCUR	VSSOP	DCU	8	3000	182.0	182.0	20.0
LSF0102DCUR	VSSOP	DCU	8	3000	180.0	180.0	18.0
LSF0102DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
LSF0102DQER	X2SON	DQE	8	5000	184.0	184.0	19.0
LSF0102YZTR	DSBGA	YZT	8	3000	182.0	182.0	20.0
LSF0108DGSR	VSSOP	DGS	20	5000	356.0	356.0	35.0
LSF0108PWR	TSSOP	PW	20	2000	364.0	364.0	27.0
LSF0108RKSR	VQFN	RKS	20	3000	202.0	201.0	28.0

GENERIC PACKAGE VIEW

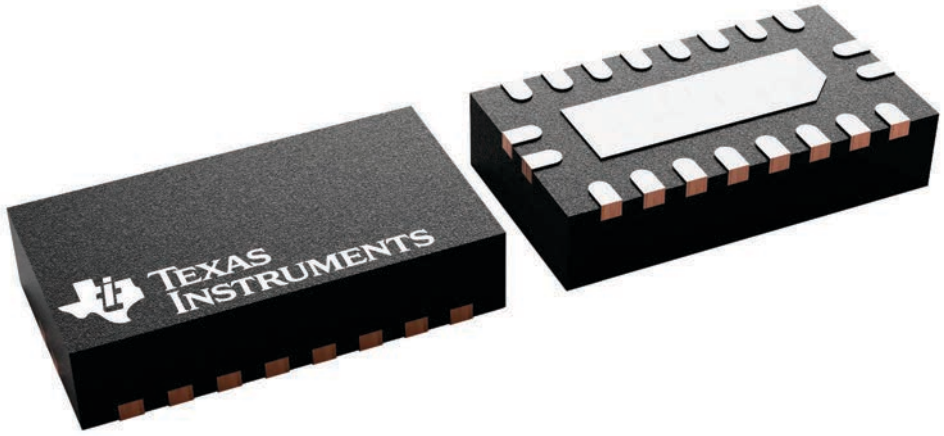
RKS 20

VQFN - 1 mm max height

2.5 x 4.5, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

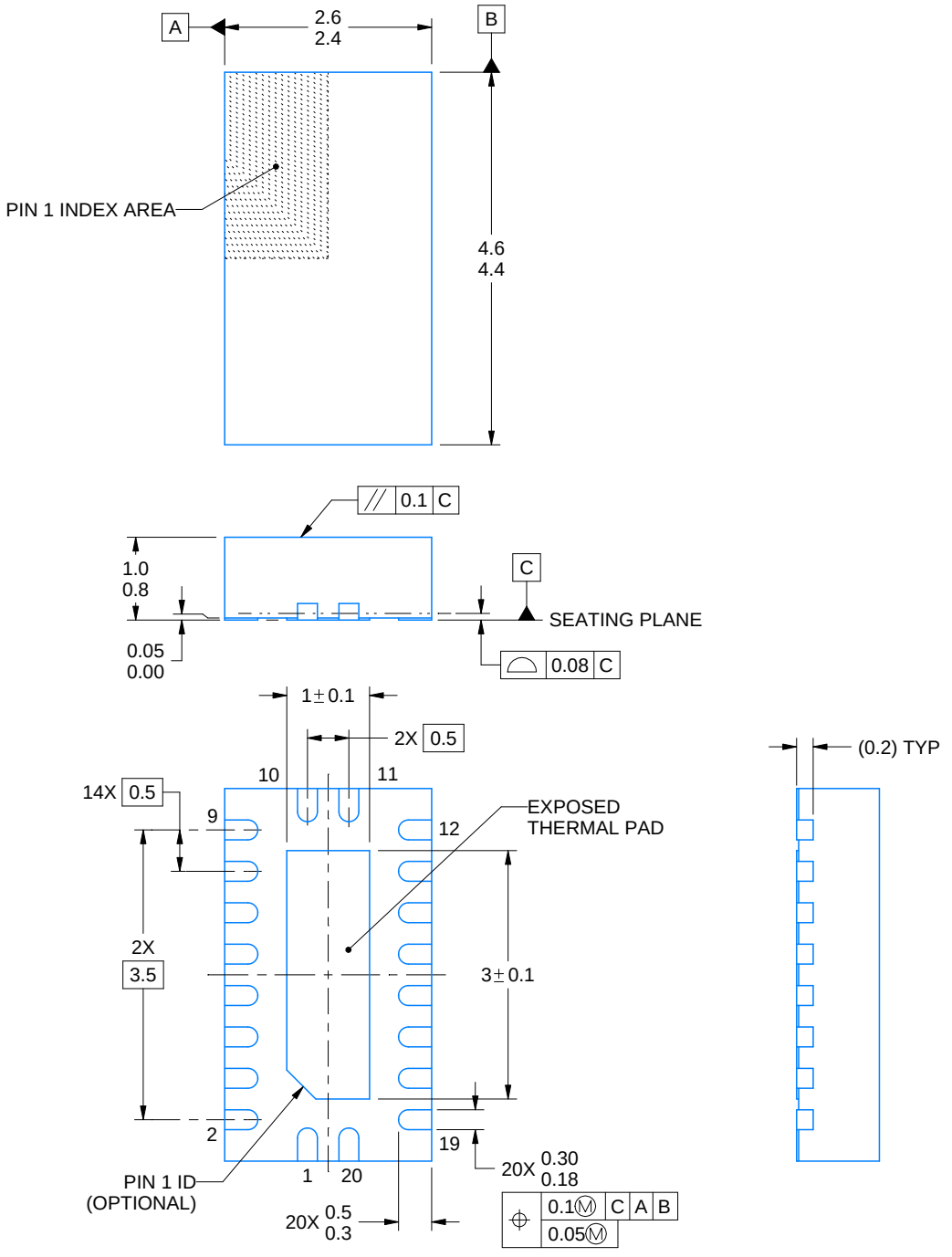


PACKAGE OUTLINE

RKS0020A

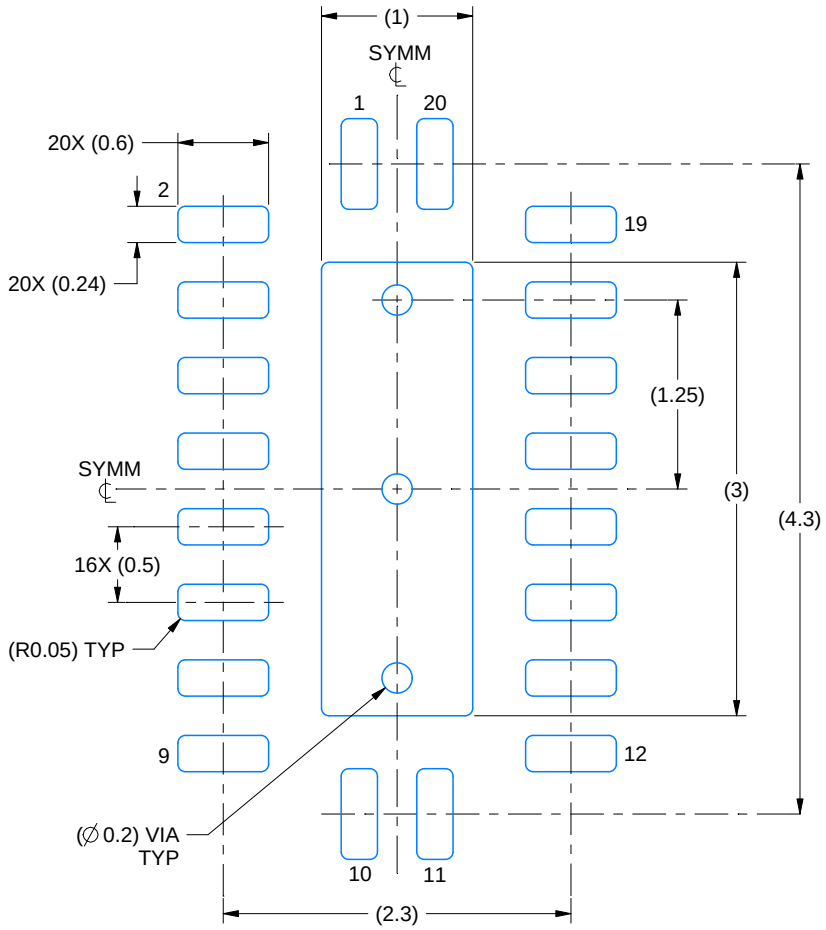
VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD

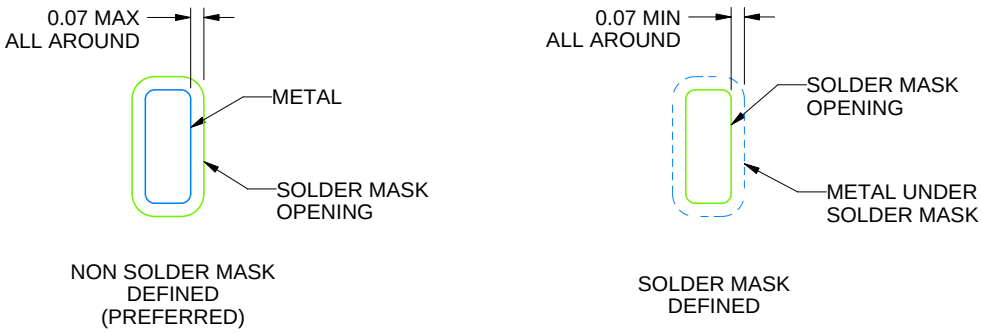


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



LAND PATTERN EXAMPLE
SCALE:20X

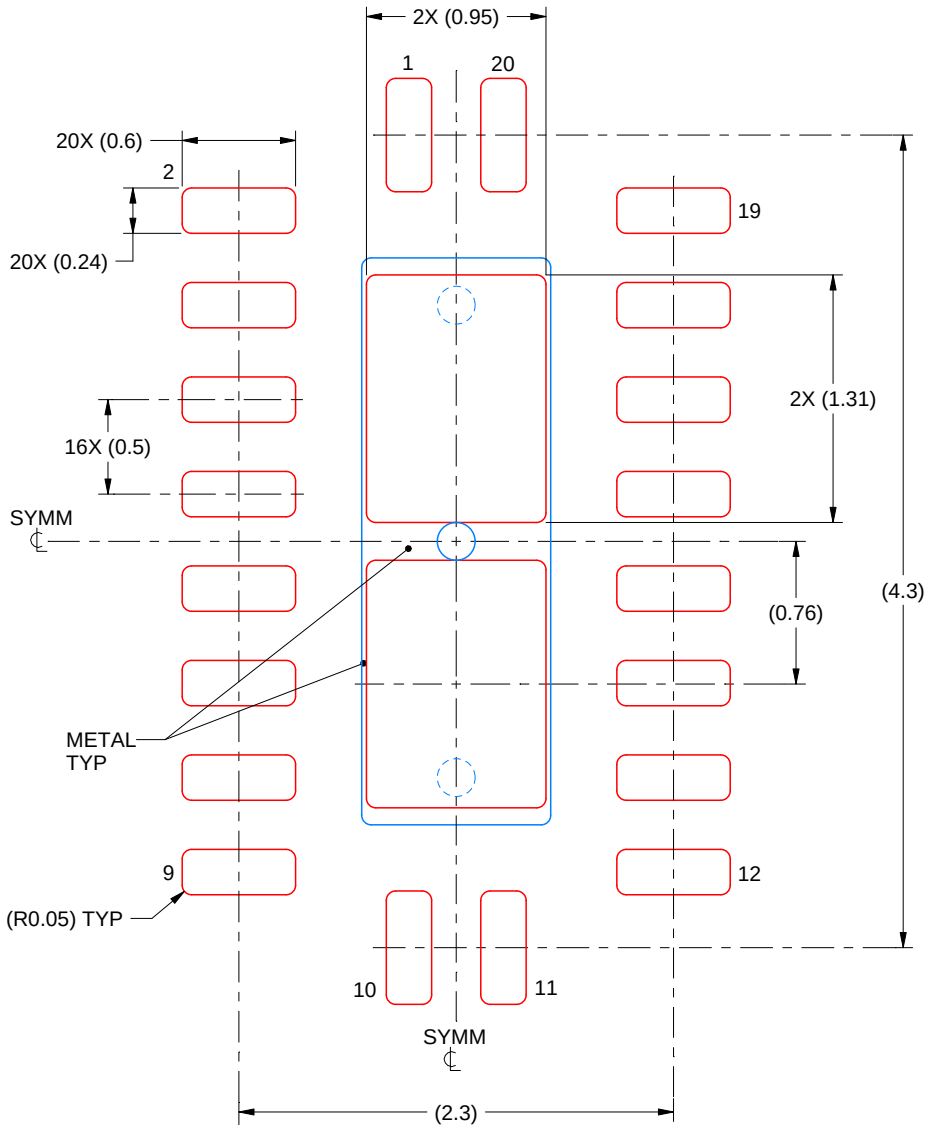


SOLDER MASK DETAILS

4222490/B 02/2021

NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD
83% PRINTED SOLDER COVERAGE BY AREA
SCALE:25X

4222490/B 02/2021

NOTES: (continued)

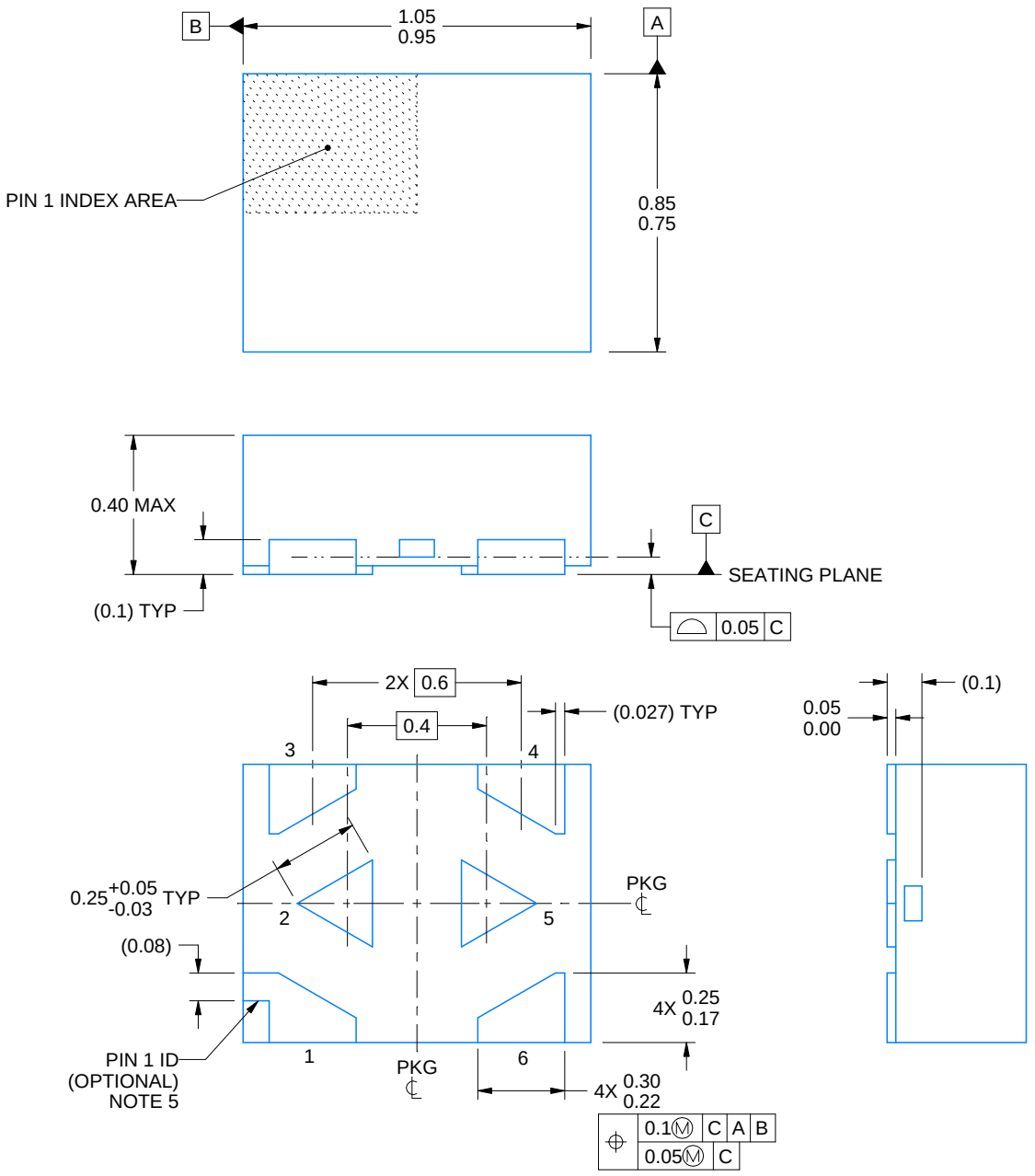
6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

DTQ0006A

PACKAGE OUTLINE

X2SON - 0.4 mm max height

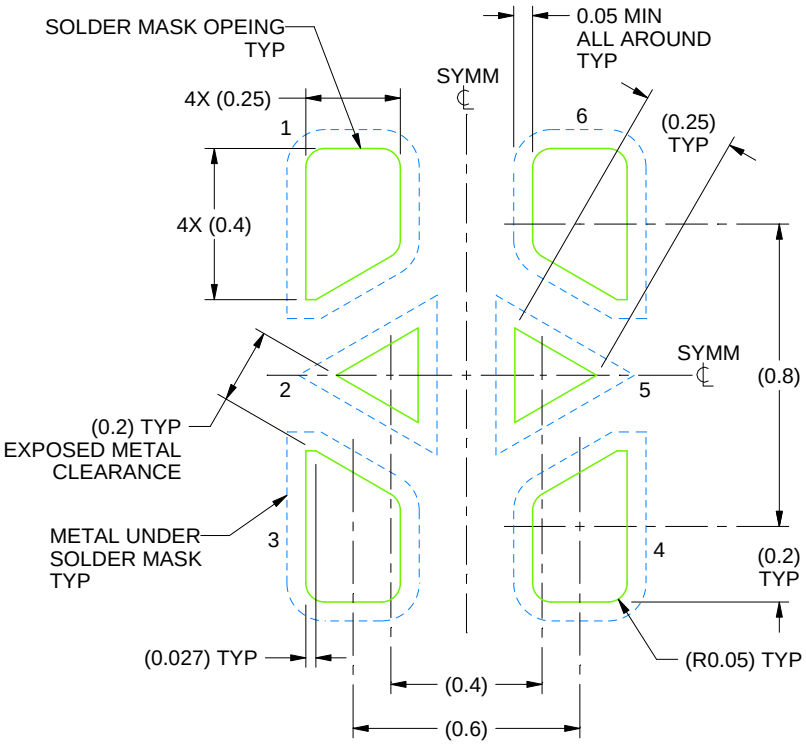
PLASTIC SMALL OUTLINE - NO LEAD



4224056/A 11/2017

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pads must be soldered to the printed circuit board for optimal thermal and mechanical performance.
4. The size and shape of this feature may vary.
5. Features may not exist. Recommend use of pin 1 marking on top of package for orientation purposes.

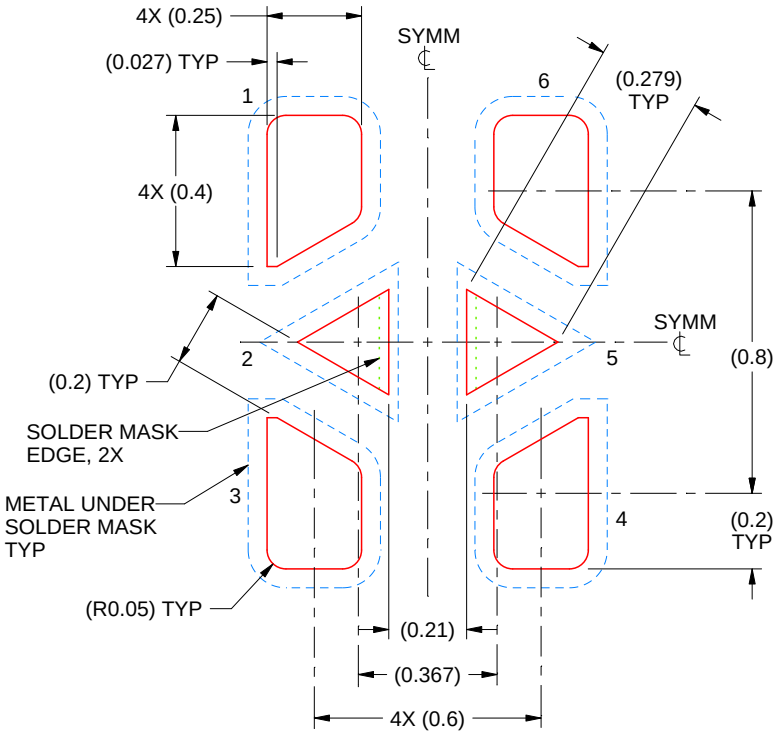


LAND PATTERN EXAMPLE
SOLDER MASK DEFINED
SCALE:50X

4224056/A 11/2017

NOTES: (continued)

6. This package is designed to be soldered to a thermal pads on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
7. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.



SOLDER PASTE EXAMPLE
BASED ON 0.07 mm THICK STENCIL

PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
SCALE:50X

4224056/A 11/2017

NOTES: (continued)

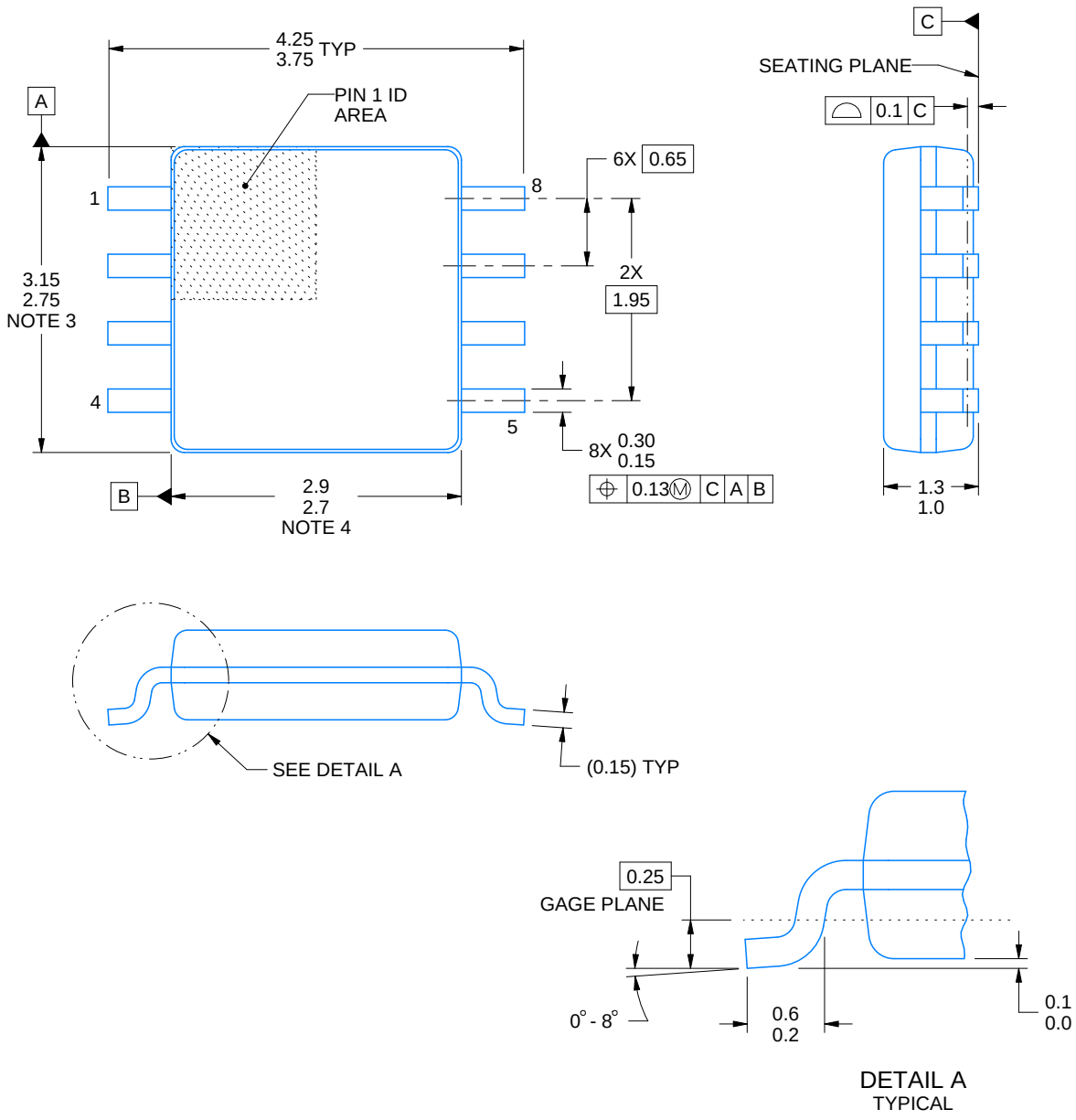
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

PACKAGE OUTLINE

DCT0008A

SSOP - 1.3 mm max height

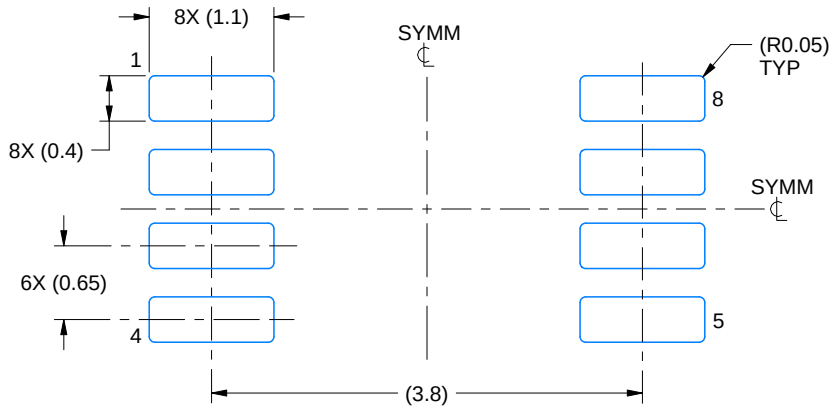
SMALL OUTLINE PACKAGE



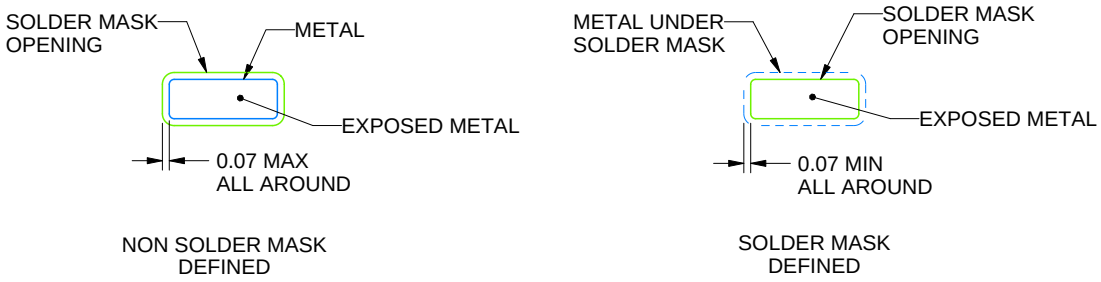
4220784/C 06/2021

NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X

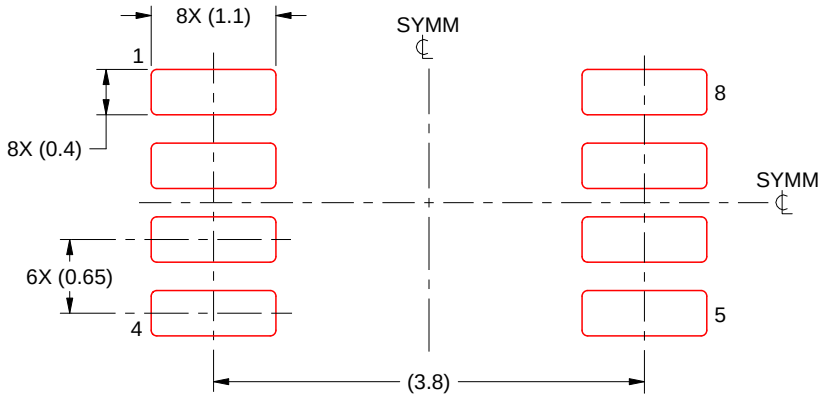


SOLDER MASK DETAILS

4220784/C 06/2021

NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

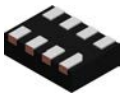
4220784/C 06/2021

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

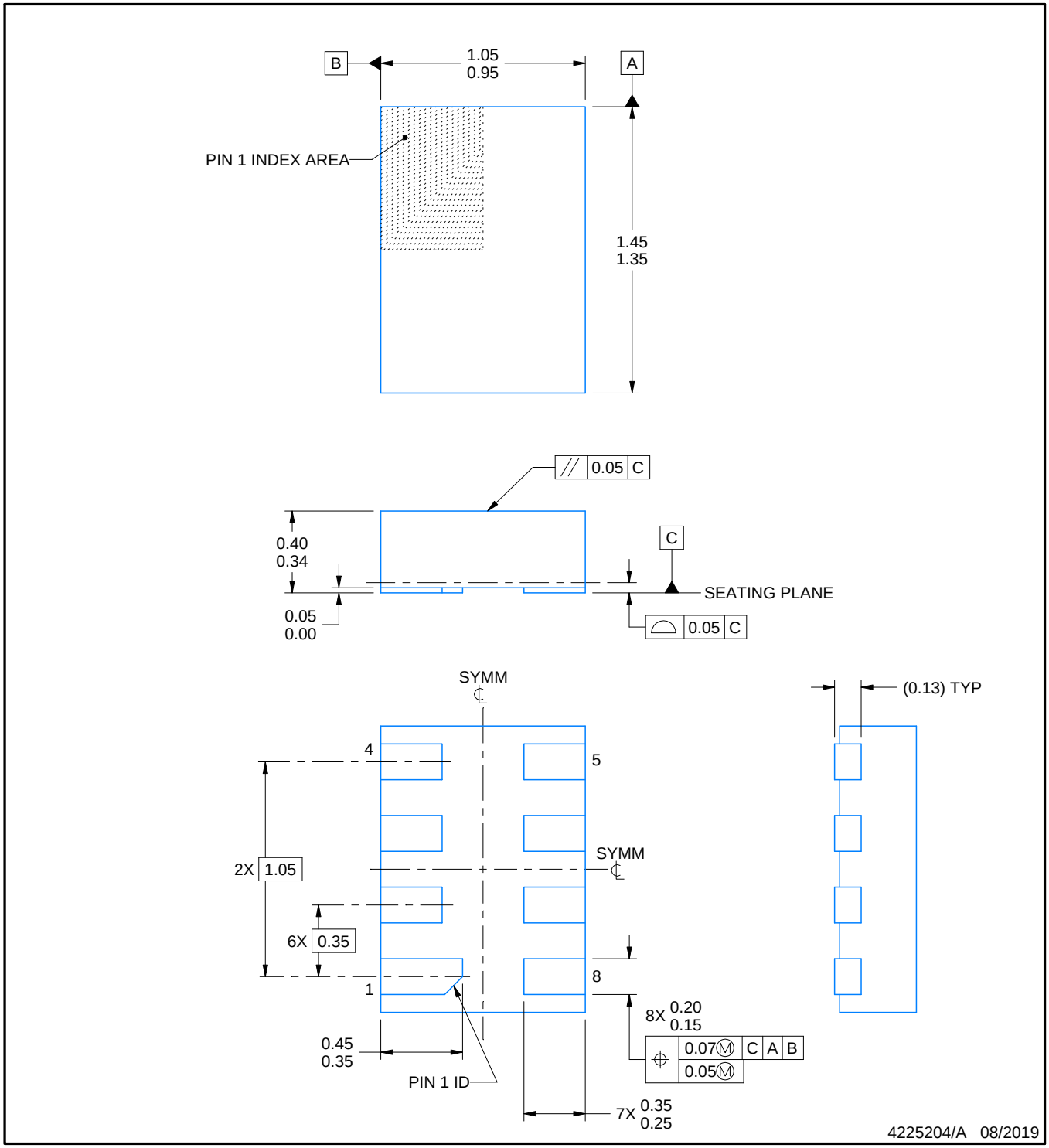
PACKAGE OUTLINE

DQE0008A



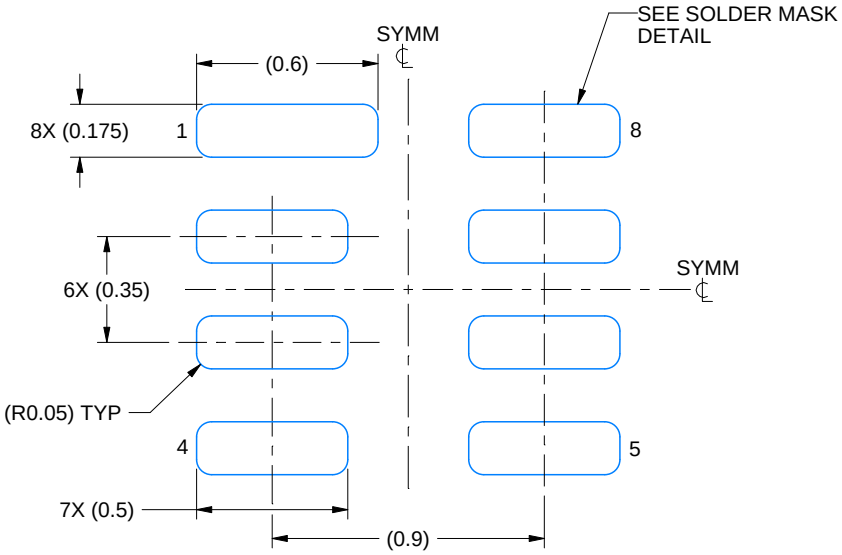
X2SON - 0.4 mm max height

PLASTIC SMALL OUTLINE - NO LEAD

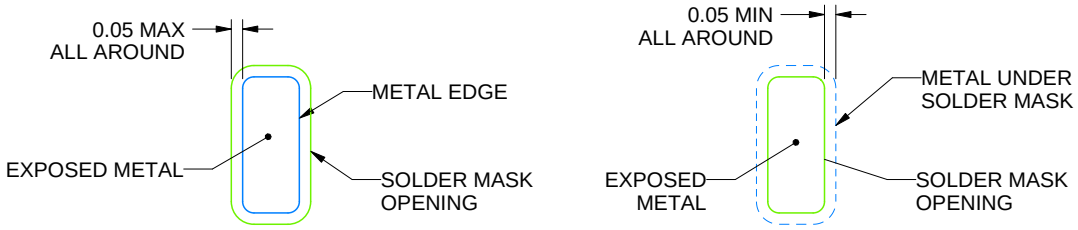


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This package complies to JEDEC MO-287 variation X2EAF.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 40X

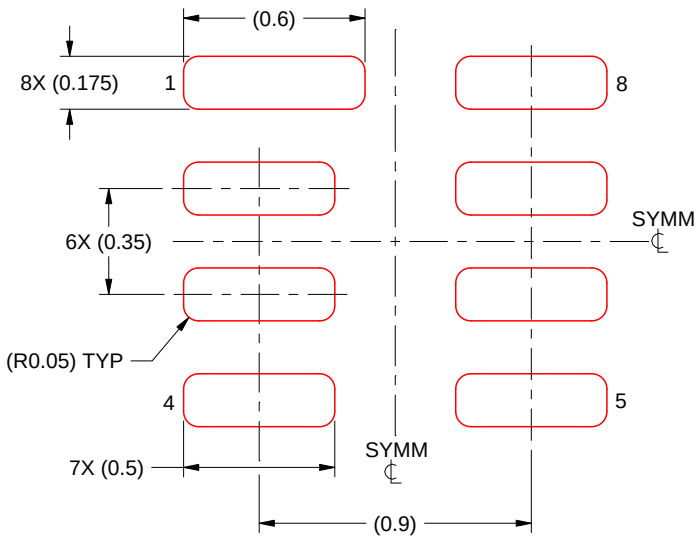


SOLDER MASK DETAILS

4225204/A 08/2019

NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).



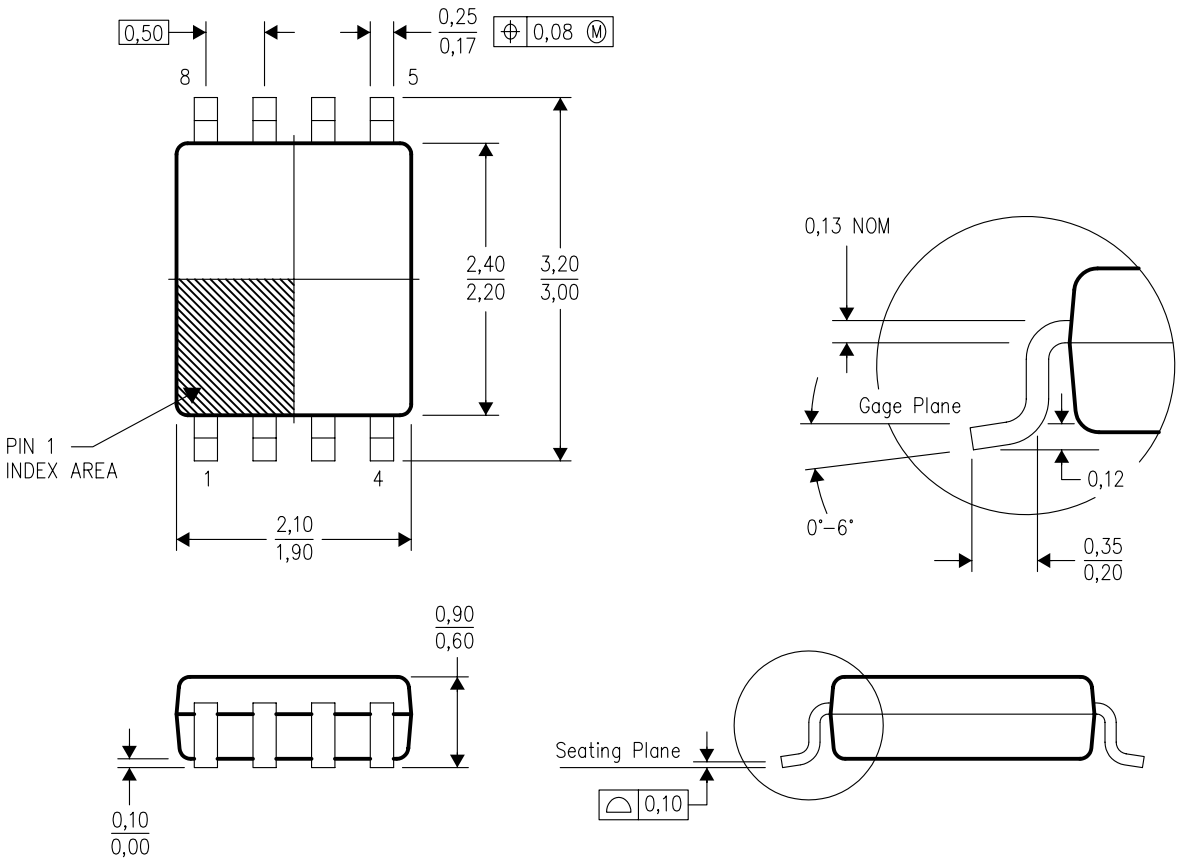
SOLDER PASTE EXAMPLE
BASED ON 0.075 MM THICK STENCIL
SCALE: 40X

4225204/A 08/2019

NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

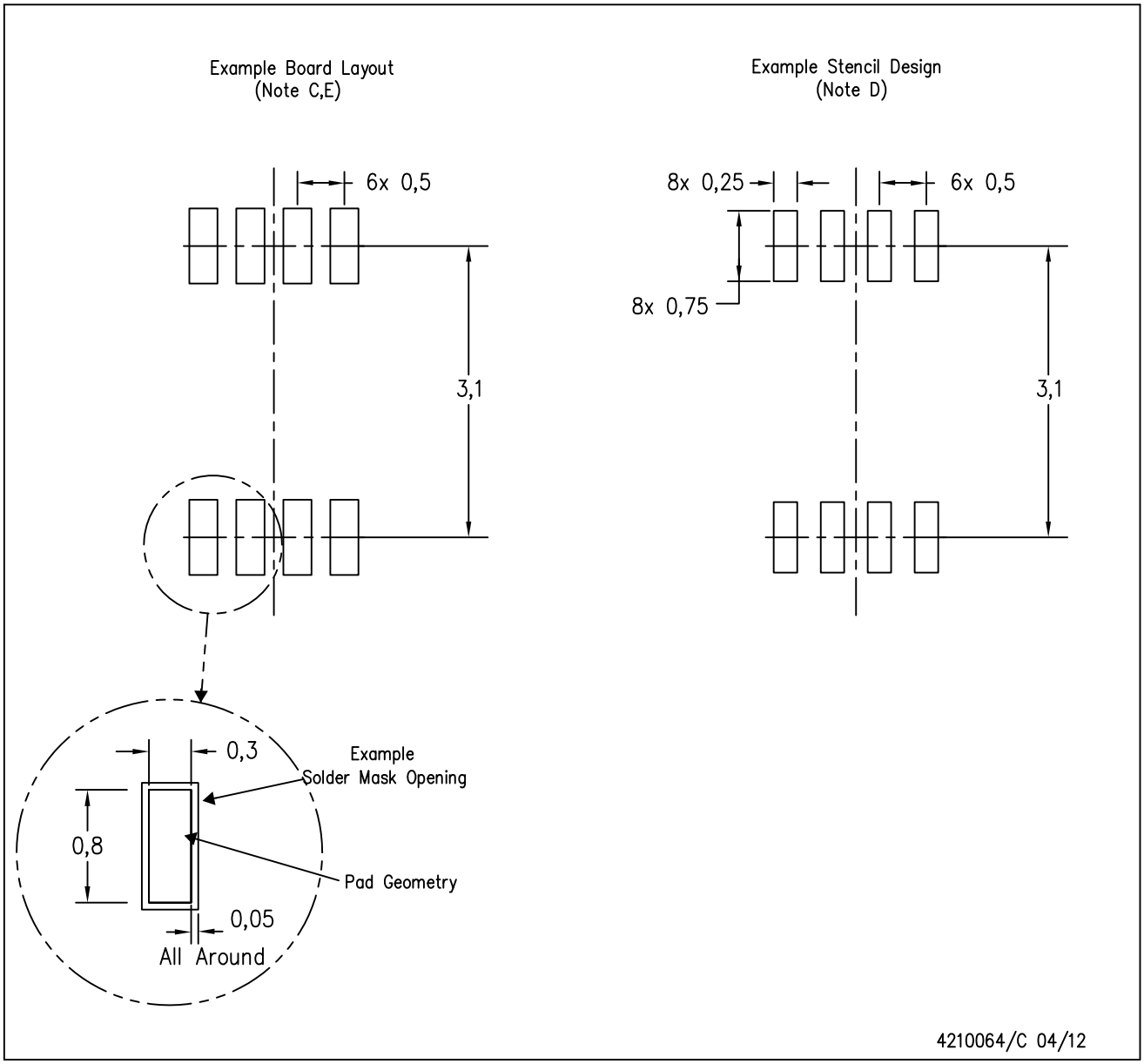
DCU (R–PDSO–G8) PLASTIC SMALL–OUTLINE PACKAGE (DIE DOWN)



4200503/F 07/05

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
D. Falls within JEDEC MO–187 variation CA.

DCU (S–PDSO–G8) PLASTIC SMALL OUTLINE PACKAGE (DIE DOWN)



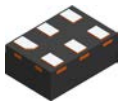
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

DRY 6 USON - 0.6 mm max height

PLASTIC SMALL OUTLINE - NO LEAD

Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

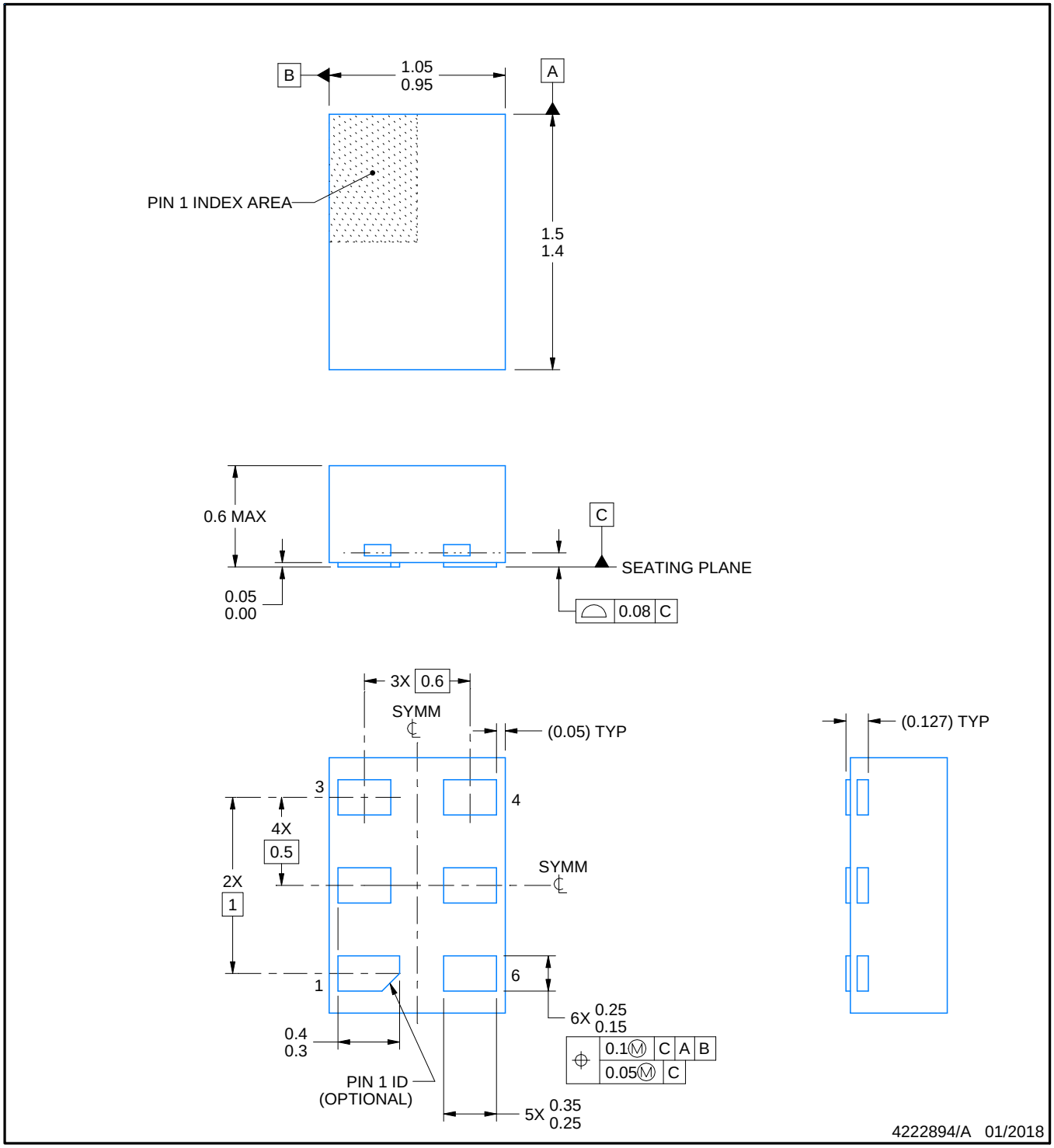
DRY0006A



PACKAGE OUTLINE

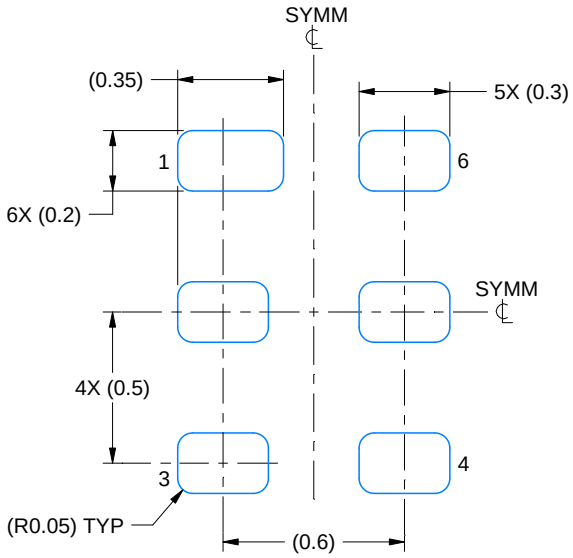
USON - 0.6 mm max height

PLASTIC SMALL OUTLINE - NO LEAD

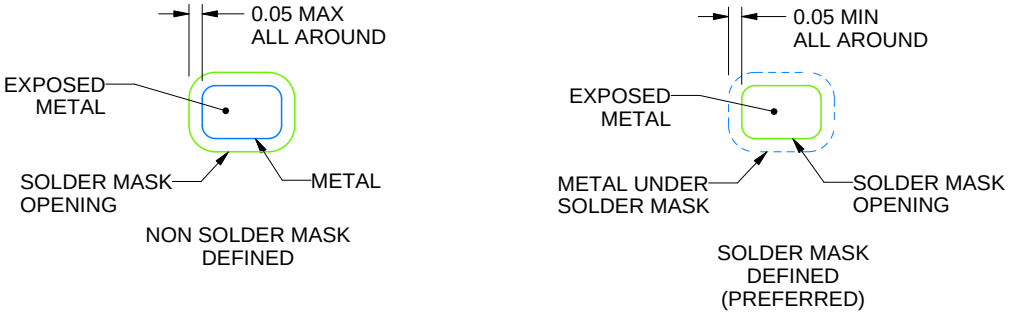


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.



LAND PATTERN EXAMPLE
1:1 RATIO WITH PKG SOLDER PADS
EXPOSED METAL SHOWN
SCALE:40X



SOLDER MASK DETAILS

4222894/A 01/2018

NOTES: (continued)

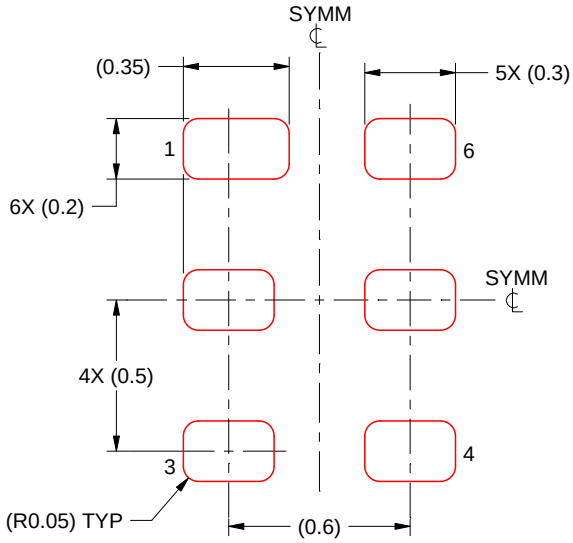
3. For more information, see QFN/SON PCB application report in literature No. SLUA271 (www.ti.com/lit/slua271).

EXAMPLE STENCIL DESIGN

DRY0006A

USON - 0.6 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.075 - 0.1 mm THICK STENCIL
SCALE:40X

4222894/A 01/2018

NOTES: (continued)

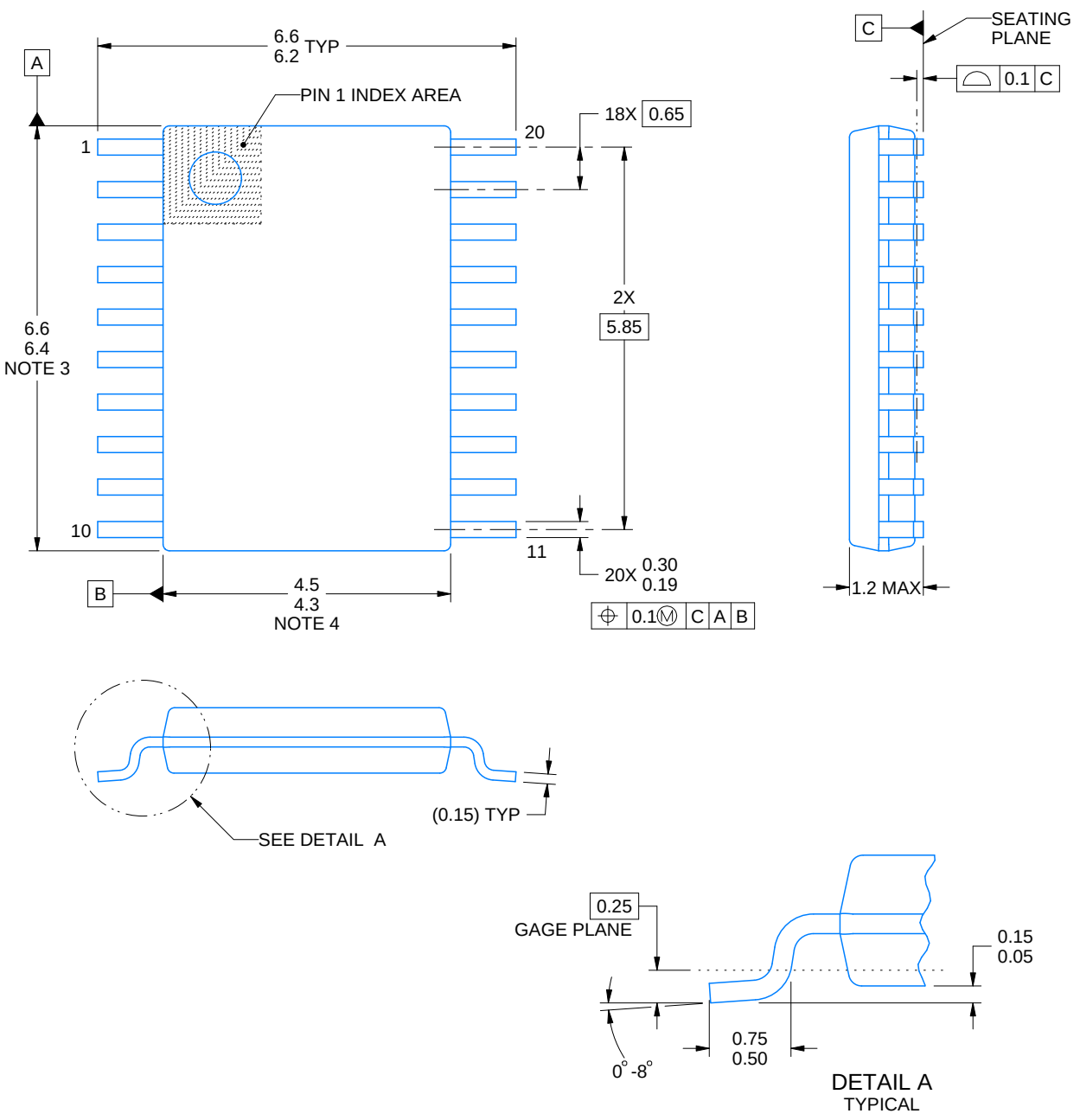
4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

PACKAGE OUTLINE

PW0020A

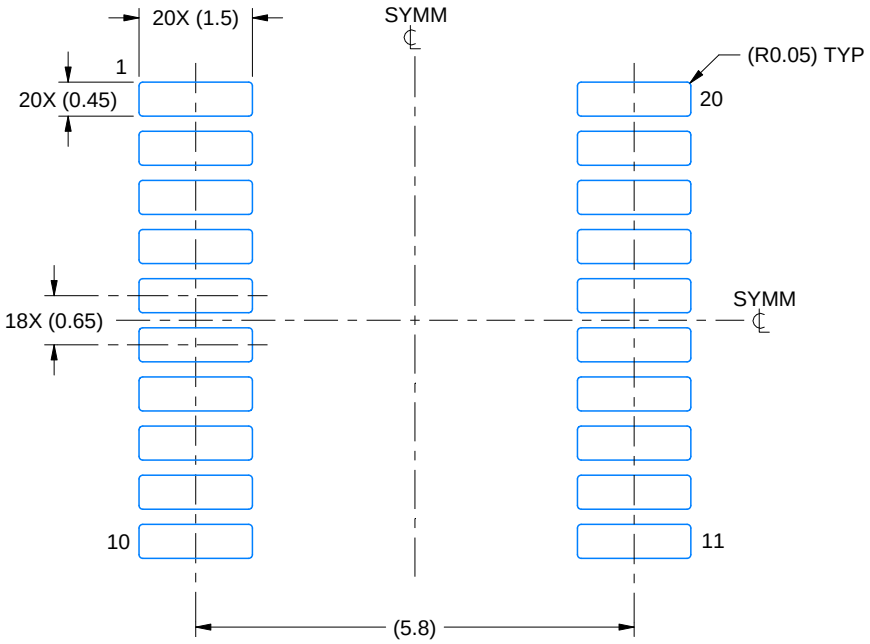
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

SOLDER MASK DETAILS

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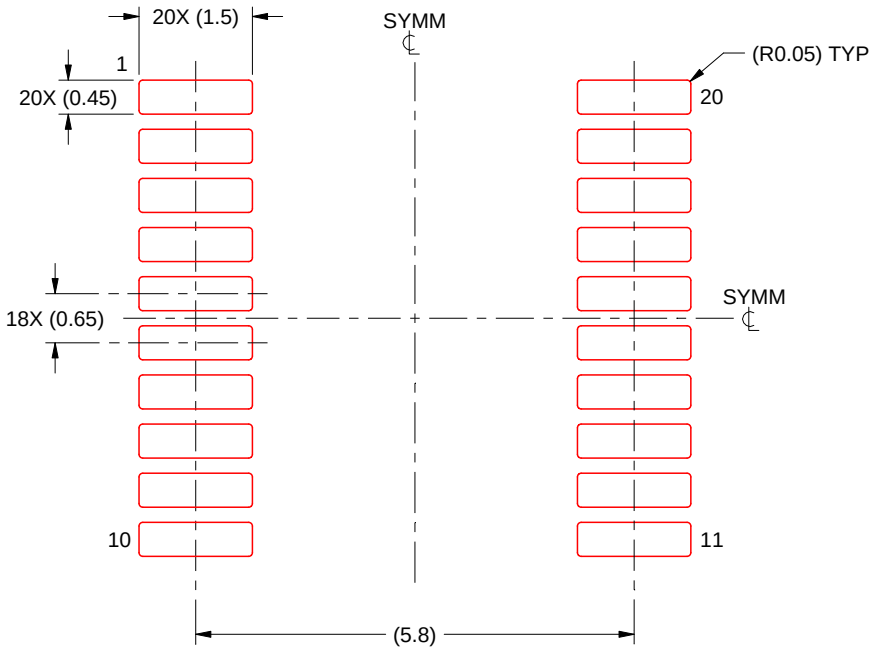
NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

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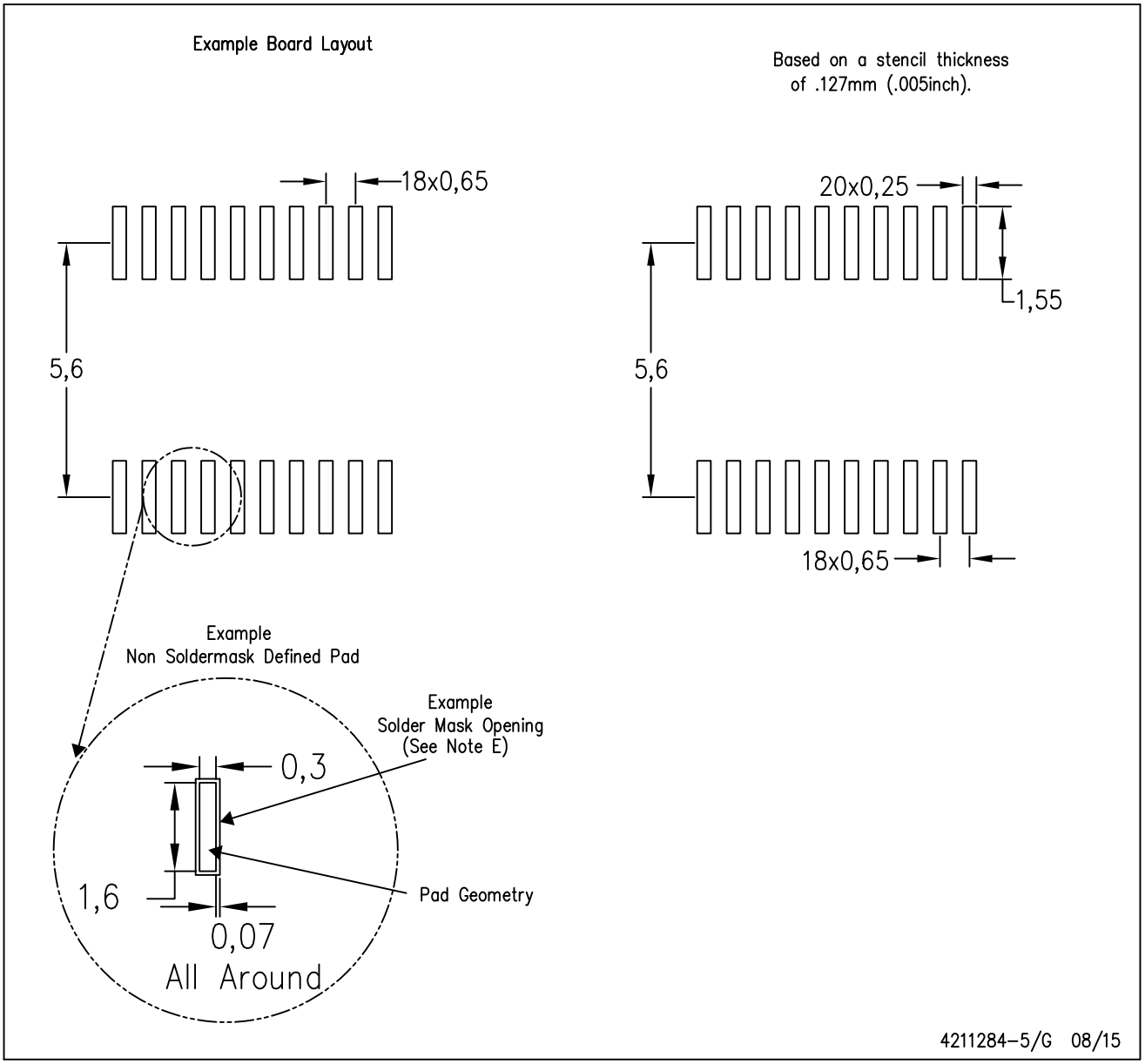
NOTES: (continued)

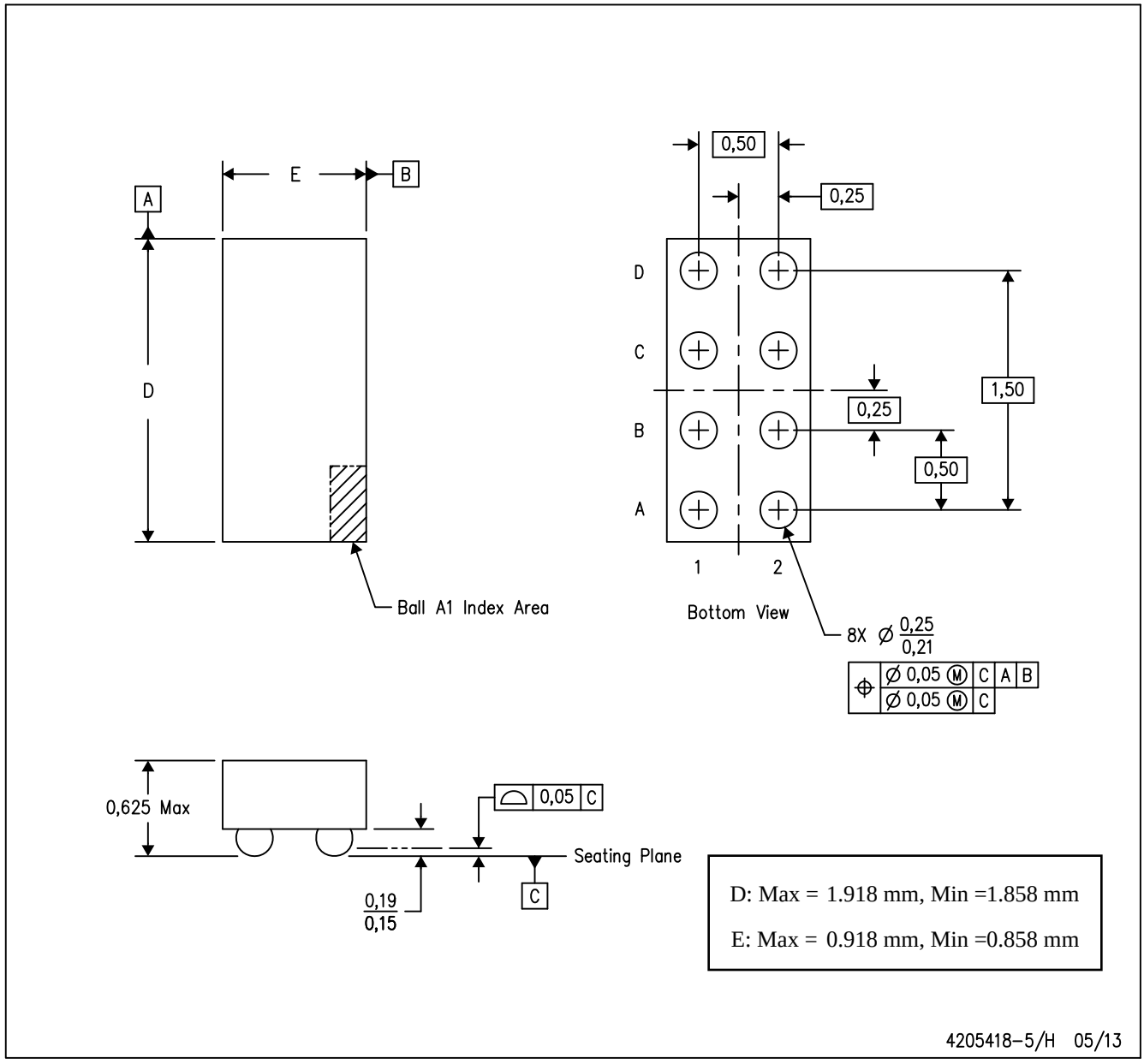
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

PW (R–PDSO–G20) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate design.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

YZT (R–XBGA–N8) DIE–SIZE BALL GRID ARRAY



NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. NanoFree™ package configuration.

NanoFree is a trademark of Texas Instruments.

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